

MANUFACTURING METHOD OF SEMICONDUCTOR INTEGRATED

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1. Field of the Invention

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2. Description of the Related Art

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a transparent quartz substrate. In other words, the photo mask is constituted in such a manner that a light screening film comprised of chromium or the like is formed in a desired shape on the quartz substrate.

5 The processing of the light screening film is carried out, for example, in the following manner: After an electron-beam-sensitive resist is applied onto the light screening film, a desired pattern is written on the electron-beam-sensitive resist by an electron beam
10 lithography system. Subsequently, after the resistor pattern of the desired shape is formed by development, the light screening film is processed by dry etching or wet etching by the use of the thus obtained resist pattern as a mask. After this, the resist is removed,
15 cleaning or the like is carried out, and thus, a light shielding pattern of a desired shape is formed on the transparent quartz substrate.

Further, recently, various mask structures have been proposed for the purpose of enhancing the
20 resolution of lithography. For example, in Japanese Patent Laid-Open No. 136854/1992, there is disclosed a mask structure constituted in such a manner that, as a means for enhancing the resolution of a single transparent pattern, the portion surrounding the
25 single transparent pattern is made semitransparent, in

other words, the light screening portion of the photo mask is made semitransparent; and thus, the phase of the slight amount of light passing through this semitransparent portion and the phase of the light passing through the transparent pattern are inverted with respect to each other. In other words, light that is below the sensitivity of the photo resist for transferring the pattern is let to pass through the semitransparent film, and the phase of this light and the phase of the light which has passed through the transparent pattern are inverted with respect to each other. The light which has passed through the semitransparent film is inverted in phase with respect to the light which has passed through the transparent pattern which is the major pattern, so that its phase is inverted in the boundary portion of the patterns, and thus, the light intensity in the boundary portion approaches 0. As a result, the ratio between the intensity of the light which has passed the transparent pattern and the intensity of the light in the pattern boundary portion becomes large; and thus, a light intensity distribution with a contrast higher than in the case of the techniques using no semitransparent film is obtained. This is called a halftone type phase shift mask. In the manufacturing

process of the halftone type phase shift mask, the light screening film of the above-mentioned ordinary photo mask is altered to a halftone phase shift film, so that the halftone type phase shift mask is
5 manufactured by approximately the same process as the above-mentioned ordinary photo mask manufacturing process.

Further, for example in Japanese Patent Laid-Open No. 289307/1993, a method of forming a light
10 screening film by the use of a resist film for the purpose of simplifying the photo mask manufacturing process and enhancing the precision. This method utilizes the properties of an ordinary electron-beam-sensitive or an ordinary light-sensitive resist that
15 it screens the vacuum ultraviolet rays with a wavelength below about 200 nm. According to this method, the step of etching the light screening film and the step of removing the resist are disused; and thus, the reduction in cost of photo masks, the
20 enhancement in dimensional accuracy thereof, and the reduction of defects thereof becomes possible.

Further, in Japanese Patent Laid-Open No. 181257/1993 for example, there is disclosed a so-called halftone mask constituted in such a manner
25 that, on a substrate which is transparent with respect

to the exposure light, a phase shift film comprising a semitransparent material which absorbs the exposure light is provided. In case of the technique disclosed in this Japanese Patent Laid-Open No. 181257/1993, the mask vacuum-holding surface is the mask substrate surface, so that exposure is executed with the mask surface directed to the exposure light source. In this case, the mechanical strength of the phase shift film comprising a semi-transparent material is high even in the periphery of the mask, and there is no problem in respect of the mask absorption and the like. Further, as for the mask alignment, the mask has light screening properties, and thus, there seems to be no problem.

Further, in Japanese Patent Laid-Open No. 15830/1997 for example, there is disclosed the technique according to which, after a light shielding pattern is formed on a mask substrate, a phase shift film is formed to a film thickness greater than the film thickness corresponding to the target phase difference, and a desired portion provided with the phase difference is etched by an amount corresponding to the target phase difference.

However, in case of the above-mentioned technique according to which the light shielding

pattern on the photo mask is formed by a resist film,
there are not disclosed the problematic point
encountered when the photo mask is actually used in
the process of manufacturing a semiconductor

5 integrated device, the problematic point encountered
in the actual photo mask manufacture, and the measures
to counter these problematic points; and the present
inventor has found that the above-mentioned technique
has the following problems.

10 More specifically, it is difficult to detect the
predetermined patterns such as, e.g., the alignment
mark, the pattern measuring mark or the product
decision mark on the photo mask, which are used for
the defection of various kinds of information. For
15 example, in case of a photo mask defect inspection
system, an aligner and the like which are used at
present, a halogen lamp or the like is mainly used for
the alignment of the photo mask. Accordingly, in case
the photo mask is mounted on a defect inspection
20 system or an aligner, if the detection mark on the
photo mask is formed by a resist film pattern, then no
high contrast can be obtained since the resist mask is
high in light transmissivity; and thus, the detection
of the pattern is difficult. Due to this, it becomes
25 difficult to align the photo mask with the defect

inspection system or the aligner, and thus, there arises the problem that no good inspection or exposure can be made.

Further, when the photo mask is mounted onto the
5 defect inspection system or the aligner, foreign
matters are produced. In case of the above-mentioned
technique, when the photo mask is mounted onto the
defect inspection system or the aligner, the resist
film of the photo mask comes into direct contact with
10 a photo mask fixing member (such as, e.g., a vacuum
fixing member) of the defect inspection system or the
aligner, so that, upon the breakage or peeling-off of
the resist film, foreign matters are produced. These
foreign matters attach to the surface of, for example,
15 the lens of the inspection system or the aligner,
contaminate the inside of the chamber or attach to the
surface of the semiconductor wafer, as a result of
which a deterioration in the inspection accuracy or
the transfer accuracy of the pattern is brought about,
20 and defects such as short-circuit or open-circuit
defects of the pattern are caused; and thus, the
reliability and manufacturing yield of the
semiconductor integrated circuit devices fall, this
being another problem.

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SUMMARY OF THE INVENTION

Thus, it is the object of the present invention to provide a method of manufacturing a semiconductor integrated circuit device using a photo mask

5 constituted in such a manner that a resist film is made to function as a light screening film, wherein the information detecting ability of the above-mentioned photo mask can be enhanced.

Further, another object of the invention is to
10 provide a method of manufacturing a semiconductor integrated circuit device using a photo mask constituted in such a manner that the resist mask is made to function as a light screening film, wherein the accuracy in the alignment of the photo mask with
15 the inspection equipment or the exposure device can be enhanced.

Still another object of the invention is to provide a method of manufacturing a semiconductor integrated circuit device using a photo mask
20 constituted in such a manner that a resist film is made to function as a light screening film, wherein the inspection accuracy of the photo mask inspection equipment.

Still another object of the invention is to
25 provide a method of manufacturing a semiconductor

integrated circuit device using a photo mask
constituted in such a manner that a resist mask is
made to function as a light screening film, wherein
the accuracy in the pattern transfer of the aligner
5 can be enhanced.

Further, still another object of the invention
is to provide a semiconductor integrated circuit
device using a photo mask constituted in such a manner
that a resist film is made to function as a light
10 screening film, wherein the occurrence of foreign
matters can be suppressed or prevented.

Further, still another object of the invention
is to provide a semiconductor integrated circuit
device using a photo mask constituted in such a manner
15 that a resist film is made function as a light
screening film, wherein the reliability and
manufacturing yield of semiconductor integrated
circuit devices can be enhanced.

The above-mentioned and other objects and novel
20 features of the present invention will be apparent
from the description in the specification and the
accompanying drawings.

Outlines of the representative ones of the
inventions disclosed in the present application will
25 be briefly described below.

According to the present invention, when an optical mask is mounted to a predetermined apparatus such as a inspection equipment or an aligner, a light shielding pattern comprising a resist film on the mask substrate of the optical mask is disposed on the major surface of the mask substrate in such a manner that the light shielding pattern and the fitting portion of the predetermined apparatus is not contacted with.

Further, according to the invention, when the optical mask is mounted onto the predetermined apparatus, a predetermined treatment is carried out on the major surface of the mask substrate of the optical mask in the state in which the fitting portion of the predetermined apparatus is contacted with a region in which the light shielding pattern comprising the resist film does not exist.

Further, according to the invention, a light shielding pattern comprising a resist film is disposed in an integrated circuit pattern region of a first mask substrate; in the outer periphery of the above-mentioned integrated circuit pattern region, a light screening metal region made of a metal is disposed; and an opening is provided in the light screening metal region, and a optical mask is used which is constituted in such a manner that a mask pattern for

detecting the information of the optical mask is formed.

Further, according to the invention, a light shielding pattern comprising a resist film is disposed
5 in an integrated circuit pattern region of a first major surface of a mask substrate; in the outer periphery of the integrated circuit pattern region, a light screening metal region comprising a metal is disposed; and further, when an optical mask
10 constituted in such a manner that an opening is provided in the light screening metal region, and a mark pattern for detecting the information of the optical mask is formed, is mounted onto an aligner, exposure light is irradiated from a second major
15 surface side of the mask substrate, in the state in which the fitting portion of the aligner is contacted with a region in which the light shielding pattern comprising a resist film does not exist; and exposure light which has transmitted through the optical mask
20 is projected by reduction exposure onto the semiconductor wafer, whereby the integrated circuit pattern is transferred onto the semiconductor wafer.

Further, according to the invention, a light shielding pattern comprising a resist film is disposed
25 on an integrated circuit pattern region of a first

major surface of a mask substrate; in the outer
periphery of the integrated circuit pattern region, a
light screening metal region made of a metal is
disposed; an opening is provided in the light
5 screening metal region, and a mark pattern for
detecting the information of the optical mask; and
further, there is used an optical mask constituted in
such a manner that a pellicle which is fixed in the
state in which the base portion of the pellicle is
10 contacted with the light screening metal region or the
mask substrate is disposed on the first major surface
side of the mask.

Further, according to the invention, when the
optical mask is mounted to the predetermined
15 apparatus, a predetermined treatment is carried out,
on the major surface of the mask substrate of the
optical mask, in the state in which the fitting
portion of the predetermined apparatus is contacted
with a region in which a halftone pattern comprising a
20 resist film does not exist.

Further, according to the invention, a light
shielding pattern comprising a resist film is disposed
in an integrated circuit pattern region on a first
major surface of the mask substrate; in the outer
25 periphery of the integrated circuit pattern region, a

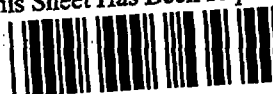
light screening metal region comprising a metal is disposed; an opening is provided in the light screening metal region, and a mark pattern for detecting the information of the optical mask; and
5 further, on the first major surface of the mask substrate, there is provided a phase shift film for causing the exposure light which has transmitted through the optical mask to produce a phase difference.

10 Further, outlines of other ones of the inventions disclosed in the present application will be briefly described below.

1. A method of manufacturing a semiconductor integrated circuit device, comprising:

- 15 (a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a second major surface side of a mask substrate, the mask substrate having on a first major surface thereof a light shielding pattern which is an integrated circuit pattern on a
20 mask and comprises a photo resist pattern; and
(b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through said mask substrate, whereby the integrated circuit pattern is imaged on a photo resist
25 film formed on a first major surface of a

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semiconductor integrated circuit wafer and thus transferred.

2. The method of manufacturing a semiconductor integrated circuit device according to Claim 1, wherein the wavelength of the exposure light is at least 100 nm less than 250 nm.

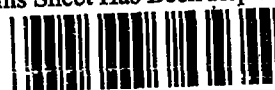
3. The method of manufacturing a semiconductor integrated circuit device according to Claim 2, wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

4. The method of manufacturing a semiconductor integrated circuit device according to Claim 3, wherein, in the peripheral portion of the first major surface of the mask substrate, a light screening metal region is provided.

5. The method of manufacturing a semiconductor integrated circuit device according to Claim 4, wherein, on the first major surface of said mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening metal region.

6. A method of manufacturing a semiconductor integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface



or a second major surface side of the mask substrate in the state in which the peripheral region of the mask substrate is held on a mask holding mechanism, the mask substrate having on the first major surface thereof a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, the resist pattern being not provided on the peripheral region; and
(b) the step of reduction-projecting, by a projection optical system, the exposure light which has transmitted through said mask substrate, whereby the integrated circuit pattern is imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer and thus transferred.

7. The method of manufacturing a semiconductor integrated circuit according to Claim 6, wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

8. The method of manufacturing a semiconductor integrated circuit according to Claim 7, wherein, wherein the wavelength of the exposure light is at least 100 nm but less than 200 nm.

9. The method of manufacturing a semiconductor integrated circuit device according to Claim 8,



wherein, in the peripheral portion of the first major surface of the mask substrate, a light screening metal region is provided.

10. The method of manufacturing a semiconductor integrated circuit device according to Claim 9, wherein, on the first major surface of the mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening metal region.

11. A method of manufacturing a semiconductor integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or second major surface side of a mask substrate, the mask substrate having, in an integrated circuit pattern region of the first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern and having a light screening metal region provided in the peripheral region of the first major surface; and

(b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through the mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the integrated



circuit pattern is imaged and thus transferred.

12. The method of manufacturing a semiconductor integrated circuit device according to Claim 11, wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

13. The method of manufacturing a semiconductor integrated circuit device according to Claim 12, wherein the wavelength of the exposure light is at least 100 nm but less than 200 nm.

14. The method of manufacturing a semiconductor integrated circuit device according to Claim 13, wherein, on the first major surface of the mask substrate, a pellicle is provided so as to cover the integrated circuit pattern, the pellicle being contact-fixed on the light screening metal region.

15. A method of manufacturing a semiconductor integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of a mask substrate, the mask substrate having, in an integrated circuit pattern region of the first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, wherein a pellicle is contact-fixed in that

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part of the peripheral portion of the integrated circuit pattern region in which the photo resist pattern is not formed so as cover said integrated circuit pattern; and

5 (b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through the mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the integrated
10 circuit pattern is imaged and thus transferred.

16. The method of manufacturing a semiconductor integrated circuit device according to Claim 15, wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

15 17. The method of manufacturing a semiconductor integrated circuit device according to Claim 16, wherein the wavelength of the exposure light is at least 100 nm but less than 200 nm.

18. The method of manufacturing a semiconductor
20 integrated circuit device according to Claim 17, wherein, in the peripheral portion of the first major surface of the mask substrate, a light screening metal region is provided.

19. The method of manufacturing a semiconductor
25 integrated circuit device according to Claim 18,



wherein, on the first major surface of said mask substrate, the pellicle is contact-fixed on said light screening metal region.

20. A method of manufacturing a semiconductor
5 integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface side or a second major surface side of a mask substrate, the mask substrate having, on the first
10 major surface thereof, a halftone light shielding pattern comprising a photo resist pattern which constitutes an integrated circuit pattern on a mask;
and

(b) the step of reduction-projecting, by a projection
15 optical system, the exposure light which has transmitted through the mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the integrated circuit pattern is imaged and thus transferred.

20 21. The method of manufacturing a semiconductor integrated circuit device according to Claim 20, wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

22. The method of manufacturing a semiconductor
25 integrated circuit device according to Claim 21,

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wherein the wavelength of the exposure light is at least 100 nm but less than 200 nm.

23. The method of manufacturing a semiconductor integrated circuit device according to Claim 22,

5 wherein, in the peripheral portion of the first major surface of the mask substrate, a light screening metal region is provided.

24. The method of manufacturing a semiconductor integrated circuit device according to Claim 23,

10 wherein, on the first major surface of the mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on the light screening region.

25. A method of manufacturing a semiconductor

15 integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface side or a second major surface side of a mask

substrate, which has, on the first major surface

20 thereof, a light shielding pattern which is an

integrated circuit pattern on a Lebenson type phase shift mask and comprises a photo resist pattern; and

(b) the step of reduction-projecting, by a projection optical system, the exposure light which has

25 transmitted through said mask substrate, whereby, on a

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first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus transferred.

26. The method of manufacturing a semiconductor
5 integrated circuit device according to Claim 25,
wherein the wavelength of the exposure light is at
least 100 nm but less than 250 nm.

27. The method of manufacturing a semiconductor
integrated circuit device according to Claim 26,
10 wherein, wherein the wavelength of the exposure light
is at least 100 nm but less than 200 nm.

28. The method of manufacturing a semiconductor
integrated circuit device according to Claim 27,
wherein, in the peripheral portion of the first major
15 surface, a light screening metal region is provided.

29. The method of manufacturing a semiconductor
integrated circuit device according to Claim 28,
wherein, on the first major surface of the mask
substrate, a pellicle is provided so as to cover said
20 integrated circuit pattern, the pellicle being
contact-fixed on the light screening metal region.

30. A method of manufacturing a semiconductor
integrated circuit device, comprising:
(a) the step of irradiating far ultraviolet or vacuum
25 ultraviolet exposure light from a first major surface

or a second major surface side of a mask substrate,
the mask substrate having, in an integrated circuit
pattern region of the first major surface thereof, a
light shielding pattern which is an integrated circuit
5 pattern on a mask and comprises a photo resist
pattern, wherein a pellicle is contact-fixed in the
peripheral portion of the integrated circuit pattern
of said first major surface so as to cover said
integrated circuit pattern; and (b) the step of
10 reduction-projecting, by a projection optical system,
the exposure light which has transmitted through the
mask substrate, whereby, on a photo resist film formed
on a first major surface of a semiconductor integrated
circuit, the integrated circuit pattern is imaged and
15 thus transferred.

31. The method of manufacturing a semiconductor
integrated circuit device according to Claim 30,
wherein the wavelength of the exposure light is at
least 100 nm but less than 250 nm.

20 32. The method of manufacturing a semiconductor
integrated Circuit device according to Claim 31,
wherein the wavelength of the exposure light is at
least 100 nm but less than 200 nm.

33. The method of manufacturing a semiconductor
25 integrated circuit device according to Claim 32,

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wherein, in the peripheral portion of the first major surface of the mask substrate, a light screening metal region is provided.

34. The method of manufacturing a semiconductor integrated circuit device according to Claim 33, wherein, on the first major surface of the mask substrate, a pellicle is provided so as to cover the integrated circuit pattern, the pellicle being contact-fixed on the light screening metal region.

35. A method of manufacturing a semiconductor integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of a mask substrate, the mask substrate having, in an integrated circuit pattern region of said first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, wherein a protective film is formed on the photo resist pattern so as to cover said integrated circuit pattern region of the first major surface; and

(b) the step of reduction-projecting, by a projection optical system, the exposure light which has been transmitted through the mask substrate, whereby, on a photo resist film formed on a first major surface of a



semiconductor integrated circuit wafer, the integrated circuit pattern is imaged and thus transferred.

36. The method of manufacturing a semiconductor integrated circuit device according to Claim 35,
5 wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

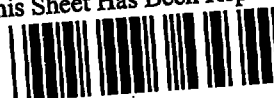
37. The method of manufacturing a semiconductor integrated circuit device according to Claim 36,
wherein the wavelength of the exposure light is at
10 least 100 nm but less than 200 nm.

38. A method of manufacturing a semiconductor integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface
15 or a second major surface side of a mask substrate, the mask substrate having, in an integrated circuit pattern region of the first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist
20 pattern, wherein a conductive ground film is formed beneath said photo resist pattern on said first major surface; and

(b) the step of reduction-projecting, by a projection optical system, said exposure light which has
25 transmitted through the mask, whereby, on a photo

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resist film formed on a first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus transferred.

5 39. The method of manufacturing a semiconductor integrated circuit device according to Claim 38, wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

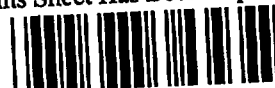
40. The method of manufacturing a semiconductor
10 integrated circuit device according to Claim 39, wherein the wavelength of the exposure light is at least 100 nm but less than 200 nm.

41. Mask blanks for the reduction projection exposure of vacuum ultraviolet rays, comprising:

15 (a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet rays or vacuum ultraviolet rays with a wavelength of at least 100 nm but less than 250 nm;

(b) a region coated with a light screening metal film
20 which region is formed on the first major surface of the mask substrate; and

(c) an opening region provided in the portion corresponding to an integrated circuit pattern region in the central portion of the region coated with a
25 light screening metal film.



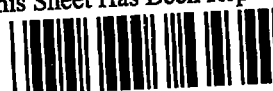
42. The method of manufacturing a semiconductor integrated circuit device according to Claim 41, wherein the wavelength of the exposure light is at least 100 nm but less than 200 nm.

- 5 43. A method of manufacturing an optical mask for performing the reduction projection exposure of a semiconductor integrated circuit device, wherein far ultraviolet rays or vacuum ultraviolet rays are used as the exposure light, comprising:
- 10 (a) the step of placing a mask substrate on a processed-mask holding portion of a mask writer;
- (b) the step of detecting a position detecting pattern provided in the peripheral portion of a first major surface of the mask substrate; and
- 15 (c) the step of calibrating an integrated circuit pattern to the position where it is to be written, on the basis of the result of the above-mentioned detection, whereby the integrated circuit pattern is written on an integrated circuit pattern region on
- 20 said first major surface.

44. The method of manufacturing a semiconductor integrated circuit device according to Claim 43, wherein the wavelength of the exposure light is at least 100 nm but less than 250 nm.

- 25 45. The method of manufacturing a semiconductor

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integrated circuit device according to Claim 44,
wherein the wavelength of the exposure light is at
least 100 nm but less than 200 nm.

46. An optical mask comprising:

- 5 (a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet or vacuum ultraviolet rays;
- (b) an integrated circuit pattern region of the first major surface of the mask substrate;
- 10 (c) an integrated circuit pattern on the mask substrate, the integrated circuit pattern being formed of a light shielding pattern in said integrated circuit pattern region of the mask substrate and being imaged on a photo resist film formed on a first major
- 15 surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through the mask substrate, the integrated circuit pattern being thus transferred; and
- 20 (d) a light screening metal region provided in the peripheral region of the first major surface of the mask substrate.

47. An optical mask comprising:

- (a) a mask substrate which has first and second major
- 25 surfaces and is transparent with respect to far



ultraviolet or vacuum ultraviolet rays;

(b) an integrated circuit pattern region of the first major surface of the mask substrate; and

(c) an integrated circuit pattern on the mask

5 substrate, the integrated circuit pattern being formed, in the integrated circuit pattern region of the mask substrate, of a halftone light shielding pattern which comprises a photo resist pattern, the integrated circuit pattern being imaged on a photo
10 resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through the mask substrate, the integrated circuit pattern being
15 thus transferred.

48. An optical mask comprising:

(a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet or vacuum ultraviolet rays;

20 (b) a Lebenson type phase shift means formed on said first major surface or second major surface;

(c) an integrated circuit pattern region of the first major surface of the mask substrate; and

(d) an integrated circuit pattern on a mask substrate,
25 the integrated circuit pattern being formed, in said



integrated circuit pattern region of the mask substrate, of a light shielding pattern which comprises a photo resist pattern, the integrated circuit pattern being imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through the mask substrate, the integrated circuit pattern being thus transferred.

49. An optical mask comprising:

(a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet rays or vacuum ultraviolet rays;

(b) an integrated circuit pattern region of the first major surface of the mask substrate;

(c) an integrated circuit pattern on the mask substrate, the integrated circuit pattern being formed, in said integrated circuit pattern region of the mask substrate, of a halftone light shielding pattern which comprises a photo resist pattern, the integrated circuit pattern being imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system,



the exposure light which has transmitted through the mask substrate, the integrated circuit pattern being thus transferred; and

- 5 (d) a protective film covering the integrated circuit pattern region and the light shielding pattern.

Further, outlines of still others of the inventions disclosed in the present application will be briefly described below.

50. The present invention comprises

- 10 (a) the step of depositing a transparent conductive film on a first major surface of a mask substrate,
(b) the step of depositing a resist film on the transparent conductive film,
(c) the step of writing a predetermined integrated
15 circuit pattern on the resist film in the state in which the transparent conductive film is grounded,
(d) the step of performing a developing treatment after the step (c), whereby a light shielding pattern constituted of the transparent conductive film and the
20 resist film is formed on the first major surface of the mask substrate,
(e) the step of holding the optical mask, which has been fabricated by the foregoing steps (a) to (d), in the state in which the light shielding pattern
25 constituted of the conductive film and the resist film

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is not contacted with the mounting portion of an aligner, and then, irradiating far ultraviolet rays or vacuum ultraviolet rays from a second major surface side of the optical mask, and

5 (f) the step of reduction-projecting by means of a projection optical system the exposure light which has transmitted through the mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the integrated
10 circuit pattern is transferred.

51. The invention comprises

(a) the step of depositing a resist film on a first major surface of a mask substrate,
(b) the step of depositing a water-soluble conductive
15 film on the resist film,
(c) the step of writing a predetermined integrated circuit pattern on the resist film in the state in which the water-soluble conductive film is grounded,
(d) the step of removing the water-soluble conductive
20 film by performing a developing treatment after the step (c), and forming a light shielding pattern, which comprises a resist film, on the first major surface of the mask substrate,
(e) the step of holding the optical mask, which has
25 been fabricated through the foregoing steps (a) to

(d), in the state in which the light shielding pattern thereof is not contacted with the mounting portion of an aligner, and then, irradiating far ultraviolet rays or vacuum ultraviolet rays from a second major surface
5 side of the optical mask, and

(f) the step of reduction-projecting by means of a projection optical system the exposure light which has transmitted through the mask substrate, whereby, onto a photo resist film formed on a first major surface of
10 a semiconductor integrated circuit wafer, the integrated circuit pattern is transferred.

52. The invention comprises

(a) the step of depositing a light screening film, which comprises a metal, on the whole of a first major
15 surface of a mask substrate,

(b) the step of patterning the light screening film to form a common light shielding pattern on the first major surface of the mask substrate,

(c) the step of depositing a resist film on the whole
20 of the first major surface of the mask substrate after the foregoing step (b), and

(d) the step of patterning the resist film, whereby a light screening pattern for transferring an integrated circuit pattern onto an integrating circuit pattern
25 region is formed on the first major surface of the

mask substrate.

53. The invention comprises

- (a) the step of depositing a resist film on a first major surface of a mask substrate and, thereafter,
5 patterning the resist film, whereby a light shielding pattern for forming an integrated circuit pattern is formed,
- (b) the step of depositing a phase shift film on the first major surface of the mask substrate after the
10 foregoing step (a),
- (c) the step of digging a groove in the phase shift film so as to produce a phase difference between the light rays which have transmitted through the mask substrate,
- 15 (d) the step of mounting, on the mounting portion of an aligner, the optical mask fabricated through the foregoing steps (a) to (c), and then, irradiating far ultraviolet rays or vacuum ultraviolet rays from a second major surface side of the optical mask, and
- 20 (e) the step of reduction-projecting by means of a projection optical system the exposure light which has transmitted through the mask substrate, whereby, onto a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the
- 25 integrated circuit pattern is transferred.

54. The invention comprises

- (a) the step of depositing a resist film on a first major surface of a mask substrate, and then, patterning this resist film to form a halftone pattern, which is
5 a pattern for forming an integrated circuit pattern and has the function of causing a phase difference between the transmitted light rays and lowering the intensity of the transmitted light rays than that of the light rays which have transmitted through the mask
10 substrate,
- (b) the step of mounting on the mounting portion of an aligner the optical mask fabricated through the foregoing step (a), and then, irradiating far ultraviolet rays or vacuum ultraviolet rays from a
15 second major surface side of the optical mask, and
- (c) the step of reduction-projecting by means of a projection optical system the exposure light which has transmitted through the mask substrate, whereby, onto
20 a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer.

55. The invention comprises

- (a) the step of depositing a resist film on a first major surface of a mask substrate, and then,
patterning this resist film to form a halftone pattern
25 which is a pattern for forming an integrated circuit

pattern and has the function of causing a phase difference between the transmitted light rays and lowering the intensity of the transmitted light rays than that of the light rays which have transmitted
5 through the mask substrate,
(b) the step of using the halftone pattern as an etching mask and digging grooves in the mask substrate exposed from therefrom, whereby the phase difference of the transmitted light rays is adjusted,
10 (c) the step of mounting on the mounting portion of an aligner the optical mask fabricated through the foregoing steps (a) and (b), and then, irradiating far ultraviolet rays or vacuum ultraviolet rays from a second major surface side of the optical mask, and
15 (d) the step of reduction-projecting by means of a projection optical system the exposure light which has transmitted through the mask substrate, whereby, onto a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the
20 integrated circuit pattern is transferred.

56. The invention comprises

(a) the step of depositing, on a first major surface of a mask substrate, a phase adjusting film for adjusting the phase of the transmitted light,
25 (b) the step of depositing a resist film on the phase

adjusting film, and then, patterning this resist film to form a halftone pattern, which is a pattern for forming an integrated circuit pattern and has the function of causing a phase difference between the transmitted light rays and lowering the intensity of the transmitted light than that of the light rays which have transmitted through the mask substrate,

5 (c) the step of using the halftone pattern as an etching mask and shaving off the phase adjusting film, which is exposed from the halftone pattern, wholly or by an amount corresponding to a predetermined thickness, whereby the phase difference of the transmitted light rays is adjusted,

10 (d) the step of mounting on the mounting portion of an aligner the optical mask fabricated through the foregoing steps (a) to (c), and then, irradiating far ultraviolet rays or vacuum ultraviolet rays from a second major surface side of the optical mask, and

15 (e) the step of reduction-projecting by means of a projection optical system the exposure light which has transmitted through the mask substrate, whereby, onto a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, the integrated circuit pattern is transferred.

20 57. The invention is constituted in such a manner.

25

that, in the preceding Item 54, 55 or 56, a light screening metal region is provided in the peripheral portion of the first major surface of the mask substrate.

5 58. The invention is constituted in such a manner that, in any one of the foregoing Items 50, 51 and 53 to 57, the wavelength of the exposure light is at least 100 nm but less than 250 nm.

59. The invention is constituted in such a manner
10 that, in any one of the foregoing Items 50, 51 and 53 to 57, the wavelength of the exposure light is at least 100 nm but less than 200 nm.

BRIEF DESCRIPTION OF THE DRAWINGS

15 Fig. 1A is a plan view of the optical mask used in the method of manufacturing a semiconductor integrated circuit device according to an embodiment of the present invention, Fig. 1B is a sectional view taken along the line A-A in Fig. 1A, and Fig. 1C is a
20 sectional view of the essential part of the optical mask, showing the state in which the optical mask shown in Fig. 1A and 1B is mounted on a predetermined apparatus.

Fig. 2A to Fig. 2C are sectional views of the
25 essential part during manufacturing steps of the

optical mask shown in Fig. 1.

Fig. 3 is a graph showing the spectral transmissivity of a typical electron beam resist film.

Fig. 4 is a sectional view of the essential part
5 of a semiconductor wafer, wherein the photo resist pattern transferred onto the semiconductor wafer by the use of the optical mask shown in Fig. 1, is symbolically shown.

Fig. 5 is an explanatory diagram of a reduction
10 projection exposure system.

Fig. 6 is a sectional view of the essential part of the semiconductor wafer during a manufacturing step for the manufacture of a semiconductor integrated circuit device.

15 Fig. 7 is a sectional view of the essential part of the semiconductor wafer during the step, which follows the step shown in Fig. 6, for the manufacture of the semiconductor integrated circuit device.

Fig. 8 is a sectional view of the essential part
20 of the semiconductor wafer during the step, which follows the step shown in Fig. 7, for the manufacture of the semiconductor integrated circuit device.

Fig. 9 is a sectional view of the essential part of the semiconductor wafer during the step, which
25 follows the step shown in Fig. 8, for the manufacture

of the semiconductor integrated circuit device.

Fig. 10A to Fig. 10C are sectional views of the essential part during manufacturing steps for the manufacture of the optical mask according to another embodiment of the present invention.

Fig. 11A to Fig. 11C are sectional views of the essential part during manufacturing steps for the manufacture of the optical mask according to still another embodiment of the invention.

Fig. 12A is a plan view of the optical mask according to still another embodiment of the invention, Fig. 12B is a sectional view taken along the line A-A in Fig. 12A, and Fig. 12C is a sectional view of the essential part of the optical mask shown in Fig. 12A and Fig. 12B, showing the state in which the optical mask is mounted on a predetermined apparatus.

Fig. 13A and Fig. 13B are flow charts showing the steps of manufacturing the optical mask shown in Fig. 12.

Fig. 14A and Fig. 14B are sectional views of the essential part during manufacturing steps for the manufacture of the optical mask shown in Fig. 12.

Fig. 15A is a plan view of the optical mask according to still another embodiment of the present

invention, and Fig. 15B is a sectional view of the essential part of the optical mask shown in Fig. 15A, showing the state in which the optical mask is mounted on a predetermined apparatus.

5 Fig. 16 is an explanatory diagram which shows the optical mask holding means when a predetermined pattern is written on an optical mask.

 Fig. 17A is a sectional view of the essential part of the optical mask according to still another
10 embodiment of the invention, and Fig. 17B is a sectional view of the essential part of the optical mask, showing the state in which, when exposure treatment is carried out, the exposure light rays which have transmitted through the respective portions
15 of the optical mask shown in Fig. 17A are phase-inverted.

 Fig. 18A to Fig. 18 C are sectional views of the essential part during manufacturing steps for the manufacture of the optical mask shown in Fig. 17.

20 Fig. 19A is a sectional view of the essential part of the optical mask according to still another embodiment of the invention, and Fig. 19B is a sectional view of the essential part of the optical mask shown in Fig. 19A, showing the state in which the
25 exposure light rays which have transmitted through the

respective portions of the optical mask are phase-inverted.

Fig. 20A is a sectional view of the essential part of the optical mask according to still another embodiment of the invention, and Fig. 20B is a sectional view of the essential part of the optical mask shown in Fig. 20A, showing the state in which the exposure light rays which have transmitted through the respective portions of the optical mask are phase-inverted.

Fig. 21A is a sectional view of the essential part of the optical mask according to still another embodiment of the invention, and Fig. 21B is a sectional view of the essential part during a manufacturing step for the manufacture of the optical mask shown in Fig. 21A.

Fig. 22A is a sectional of the essential part of the optical mask according to still another embodiment of the invention, and Fig. 22B is a sectional view of the essential part during a manufacturing step for the manufacture of the optical mask shown in Fig. 22B.

Fig. 23A to Fig. 23D are sectional views of the essential part during manufacturing steps for the manufacture of the optical mask according to still another embodiment of the invention.

Fig. 24A is a sectional view of the essential part of the optical mask according to still another embodiment, and Fig. 24B is a sectional view of the essential part of the optical mask shown in Fig. 24A, showing the state in which the optical mask is mounted onto a predetermined apparatus.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Before giving a detailed description of the present invention, the meanings of some terms used in the present application will first be explained.

1. Device surface means a major surface of a semiconductor wafer, on which a device pattern corresponding to a plurality of chip regions is formed by photolithography.

2. Semiconductor integrated circuit wafer (semiconductor integrated circuit substrate) or semiconductor wafer (semiconductor substrate) means a monocrystalline silicon substrate (generally, in an approximately plane, circular shape), a sapphire substrate, a glass substrate or another insulating, semi-insulating or semiconductor substrate or a composite substrate comprising them, which is used for the manufacture of a semiconductor integrated circuit.

3. Organic SOG (Spin On Glass) is generally an

interlayer dielectric film material which is formed in such a manner that a high-molecular resin in which various organofunctional groups are bonded to a siloxane polymer or a copolymer prepared from siloxane polymer and another monomer is dissolved in a solvent and spin-coated on a semiconductor wafer. In general, the organic SOG has the feature that, unlike in case of the inorganic SOG, cracks are hard to be caused therein after its curing, so that the organic SOG film can be formed somewhat thick. Among the organic siloxane series interlayer film materials, there are some which are formed into films by the CVD (Chemical Vapor Deposition).

4. When etching stopper is mentioned, an etching stopper whose etching selective ratio to the concerned etching stopper film is 4 or higher is referred to (in case it is mentioned that the etching selective ratio of A to B is X, it means that the etching rate of A is X, and the etching rate of B is 1). As etching stopper films, coated stopper films and the like are also included.

5. Masking layers generally means resist films but, here, include inorganic masks, non-photosensitive organic masks and the like, too.

6. When "light screening region", "light

screening film" or "light shielding pattern" is mentioned, it indicates that the above-mentioned region has the optical characteristic that, of the exposure light irradiated to the region, less than 40% is allowed to transmit through the region. In general, what allows 30% or less of the exposure light to transmit through the region is used. On the other hand, when "transparent" and "transparent film" are mentioned, it indicates that the film has the optical characteristic that, of the exposure light irradiated to the concerned region, 60% or more is allowed to transmit through it. In general, what allows 90% or more of such irradiated exposure light to transmit through it is used.

7. "Photo resist pattern" means a film pattern obtained by patterning a photosensitive organic film by the photolithography technique. In addition, as such photo resist pattern, a mere resist film which has no opening at all with respect to the portion concerned is also included.

8. The pattern surface of a mask is divided into the following regions: The region in which the integrated circuit pattern transferred is disposed "integrated circuit pattern region", the region covered with a pellicle "pellicle-covering region",



the pellicle-covering region other than the integrated circuit pattern region "peripheral region of the circuit pattern", the external region covered with no pellicle "peripheral region", the inner region of the peripheral region in which an optical pattern is formed "inner peripheral region", and the other portion of the peripheral region which is used for vacuum suction or the like "outer peripheral region".

9. In the field of semiconductors, ultraviolet rays are divided as follows: Ultraviolet rays which have a wavelength less than about 400 nm but higher than about 50 nm are called ultraviolet rays, rays which have a wavelength of 300 nm or higher are called near ultraviolet rays, rays having a wavelength less than 300 nm but higher than 200 nm are called far ultraviolet rays, and rays which have a wavelength 200 nm or less are called vacuum ultraviolet rays. Main embodiments of the present invention have been described with respect mainly to the vacuum ultraviolet range with a wavelength of 200 nm or less, but, if alteration is made as described with reference to the following embodiments, then it is a matter of course that the present invention is applicable even in case of the far ultraviolet range based on an KrF excimer laser having a wavelength less than 250 nm but

higher than 200 nm. Further, it is also possible to apply the principle of the present invention even to the shortest wavelength end range of the ultraviolet rays having a wavelength less than 100 nm but higher than 50 nm.

10. When "metal" is mentioned concerning the mask light-screening material, chromium, chromium oxide and similar compounds of other metals are meant; and, from a wider viewpoint, single substances, compounds, and composites which each contain a metal element and have a light screening function are also included.

11. "Halftone mask" is a kind of phase shift mask and has a halftone shifter in which the Transmissivity of the halftone film serving as a shifter and also as a light screening film is at least 1% but less than 40%, and the phase shift amount thereof as compared with the portion in which no halftone shifter inverts the phase of the light.

12. "Levenson type phase shift mask" is a kind of phase shift mask constituted in such a manner that the phases of openings adjacent to each other but separated from each other by a light screening region are inverted with respect to each other, so that, by the interference action thereof, a clear picture is

intended to be obtained.

In the following embodiments, description will be made, if required, by dividing each embodiment into a plurality of sections or embodiments for
5 convenience's sake, but, unless particularly specified, they are not irrelevant to each other; but each is in a relationship of being a modification of a part or the whole of the other or a detailed or supplementary explanation of the other.

10 Further, in the following embodiments, in case of referring to the number and the like (including the number of individual elements, numerical value, amount, range, etc.) of elements, the invention is not limited to the specific number, but can be more or
15 less than the specific number, unless otherwise specified and except for cases such as the case where it is clear in view of the principle that limitation is made to a specific number.

Further, in the following embodiments, it is a
20 matter of course that the constitutional elements (including the element steps etc.) of the embodiments are not always indispensable unless otherwise specified and excepting cases such as the case where it is considered that, in view of the principle, the
25 constitutional elements are clearly indispensable).

Similarly, in the following embodiments, when the shape, the positional relationship, etc. of a constitutional element are referred to, those which are substantially approximate or similar to the particular shape and the like are included unless otherwise specified and excepting cases such as the case where it is considered, in view of the principle, that it is clearly not so. The same thing applies also to the above-mentioned numerical value and range.

Further, when semiconductor integrated circuit device is referred to in the present specification, it is to be considered that not only device made on a semiconductor or insulator substrate such as a silicon wafer, a sapphire substrate or the like, but also a TFT (Tin-Film-Transistor) and the device made on another insulating substrate made of glass such as STN (Super-Twisted-Nematic) liquid crystal or the like are also included.

The embodiments of the present invention will now be described in detail on the basis of the drawings. In all the drawings for explaining the embodiments, the elements which have the same functions are referenced by the same reference numerals and symbols, whereby the repetition of the description thereof is omitted. Further, in the

embodiments of the invention, a p-channel type MISFET (Metal Insulator Semiconductor Field Effect Transistor) will be abbreviated to pMIS, while an n-channel type MISFET will be abbreviated to nMIS.

5

Embodiment 1:

Fig. 1A is a plan view of the photo mask used for the method of manufacturing a semiconductor integrated circuit device according to an embodiment of the invention, Fig. 1B is a sectional view taken along the line A-A in Fig. 1A, and Fig. 1C is a sectional view of the photo mask shown in Fig. 1A and Fig. 1B, showing the state in which the photo mask is mounted on a predetermined apparatus. The broken lines in Fig. 1A are provided for easier understanding of the description, but not formed in the actual product.

The photo mask 1PA1 according to this Embodiment 1 is a reticle for imaging and transferring onto a semiconductor wafer the original picture of a semiconductor integrated circuit pattern, which is for example five times as large as the actual dimensions, through a reduction projection optical system or the like; this reticle is used in a projection aligner using as a light source vacuum ultraviolet rays such

as, e.g., a argon fluoride (ArF) excimer laser beam (with a wavelength of 193 nm) or a fluorine gas (F₂) laser beam (with a wavelength of 157 nm).

A mask substrate 1a constituting this photo mask 1PA1 comprises, for example, a transparent synthetic quartz glass or the like formed into a square shape. The region surrounded by the innermost broken line in Fig. 1A shows the above-mentioned integrated circuit pattern region. In this integrated circuit pattern region, a light shielding pattern 1b for transferring the integrated circuit pattern onto a semiconductor wafer. In this Embodiment 1, the light shielding pattern 1b is formed of a resist film. The structural details such as the material and the thickness of this resist film will be described later.

The region lying outside this integrated circuit pattern region is the peripheral region of the above-mentioned integrated circuit pattern. Of this peripheral region, the region surrounded by the broken line outside the integrated circuit pattern region is the region corresponding to the above-mentioned inner peripheral region, where a mark pattern 1mr for detecting the information of the photo mask 1PA1 is formed. In this Embodiment 1, this mark pattern 1mr is also formed of the above-mentioned resist film. As

this mark pattern lmr, there are, for example, an aligning mark and a calibrating mark used for the photo mask manufacture. The aligning mark is a mark used for making the alignment between the photo mask 1PA1 and an inspection equipment or an aligner so that the aligning mask inspect the position of the photo mask 1PA1 at the time of mounting the photo mask 1PA1 onto "predetermined apparatus of the inspection equipment or the aligner. Further, the calibrating mark is a mark used for measuring the misalignment, the shape state of the pattern or the pattern transfer accuracy. The mark pattern lmr is a pattern which is not transferred onto the semiconductor wafer.

Further, the region lying outside this inner peripheral region is the above-mentioned outer peripheral region through which, at the time of mounting the photo mask 1PA1 onto a mounting portion 2 of the inspection equipment or the aligner, the photo mask 1PA1 comes into direct contact with the mounting portion 2. In this Embodiment 1, a pattern forming resist film is not formed in the outer peripheral region. If a resist film is formed in this outer peripheral region, then, when the photo mask 1PA1 is mounted onto the inspection equipment or the aligner, the above-mentioned resist film is peeled off or

shaven off, as a result of which foreign matters are produced; but, in this Embodiment 1, no resist film is formed in the outer peripheral region, so that inconveniences such as the peeling-off of the resist film due to mechanical shocks and the production of foreign matters could be prevented. As the mounting portion 2, a mounting portion with a vacuum holding mechanism is shown by way of example.

Next, an example of the method for the manufacture of the photo mask 1PA1 shown in Fig. 1 will be described.

First, as shown in Fig. 2A, a mask substrate 1a comprising a transparent synthetic quartz substrate with a thickness of, e.g., about 6 mm is prepared, and then, as shown in Fig. 2B, a resist film 1R which has the properties of absorbing vacuum ultraviolet rays such as, e.g., an ArF excimer laser beam or an F₂ laser beam is applied over the whole of a major surface of the mask substrate 1a by the spin-coat method or the like. This resist film 1R is a resist film which is sensitive to an electron beam. Here, a novolac series resist film was formed to a thickness of, e.g., about 150 nm.

Subsequently, as shown in Fig. 2C, the light shielding pattern 1b and the mark pattern 1mr each

comprising a resist film were formed by the same method as the method of forming a desired pattern in an ordinary photo mask manufacturing process. Here, a measure to counter the charging of the electron beam, which will be described later, was taken. Further, the peripheral portion of the photo mask 1PA1 will serve as a portion contacted with the projection aligner, so that the resist film was removed; and thus, the occurrence of foreign matters due to the peeling-off or the shaving-off of the resist film was prevented.

For this resist film 1R, a material composed mainly of, e.g., a copolymer of α -methylstyrene and α -chloroacrylic acid, novolac resin and guanine diazide, novolac resin and polymethyl pentene-1-sulfone, or chloromethylated polystyrene was used. A so-called chemically amplified resist composed by incorporating an inhibitor and an acid generating agent into a phenol resin or a novolac resin can be used. As the material of the resist film 1R used here must have a light screening characteristic with respect to the light source of the projection aligner and also have the characteristic of having sensitivity to the light source of the pattern lithography system, in the photo mask manufacturing process, such as, e.g., an electron

beam or light with a wavelength of 230 nm or higher;
the material of the resist film IR is not limited to
the above-mentioned materials but can be variously
altered. Further, the film thickness is not limited
5 to 150 nm, either, but can be a value which can
satisfy the above-mentioned condition.

Fig. 3 shows the spectral Transmissivity of a
typical electron beam resist film. In case a
polyphenol series resin or a novolac series resin is
10 formed into a film thickness of about 100 nm, its
transmissivity is approximately zero at a wavelength
of, e.g., about 150 to 230 nm; the electron beam
resist film exhibits a sufficient mask effect with
respect to an ArF excimer laser beam with a wavelength
15 of 193 nm, an F₂ laser beam with a wavelength of 157
nm, and the like. Here, vacuum ultraviolet rays with
a wavelength of 200 nm or less are employed, but the
present invention is not limited to this.

As the mask material for the KrF excimer laser
20 beam or the like with a wavelength of 248 nm, it is
necessary to use other material or to add an absorbing
agent into the resist film. Further, after the light
shielding pattern lb and the mark pattern lmr
comprised of a resist film are formed, it is effective
25 to subject the resist film to a so-called hardening

treatment performed by adding a heat treatment step or powerfully irradiating ultraviolet rays previously, for the purpose of enhancing the resistance to the exposure light irradiation. Further, for the purpose of preventing the oxidation of the resist film, it is also effective to keep the pattern surface in an atmosphere of an inert gas such as, e.g., nitrogen (N_2). Further, as the pattern writing of the resist film, not only the electron beam writing but also the pattern writing by ultraviolet rays with a wavelength of, e.g., 230 nm or higher can also be applied. The spirit of the present invention lies in using the resist film directly as the mask and providing a practically usable mask structure. Accordingly, as the wavelength to be screened, the resist material and the mask substrate material, other wavelengths and materials may also be used.

By the use of this photo mask 1PA1, the pattern was transferred by a reduction projection exposure system. As the projection light of the reduction projection exposure system, an ArF excimer laser beam with a wavelength of, e.g., about 193 nm was used; the numerical aperture NA of the projection lens was for example about 0.68; the coherence σ of the light source used was for example 0.7. On the semiconductor

wafer which would be used as a projected substrate, an ordinary positive resist film with a sensitivity to ArF was formed to a thickness of, e.g., about 300 nm. The alignment between the reduction projection exposure system and the photo mask 1PA1 was made by detecting the mark pattern 1mr formed on the photo mask 1PA1. For this alignment, a helium-neon (He-Ne) laser beam with a wavelength of, e.g., 633 nm was used. Due to this, the mark pattern 1mr constituted of a resist film has no light screening effect, and thus, the contrast between the light which has transmitted through the mark pattern 1mr and the light which has transmitted through the light transmitting portion cannot be obtained. Thus, the scattered light at the edge of the mark pattern 1mr was detected. As a result, as shown in Fig. 4, the semiconductor integrated circuit pattern on the photo mask 1PA1 was projected onto a major surface (first major surface) of a semiconductor wafer 3, and ordinary heat treatment and developing steps were carried out to form a resist pattern 4. As a result, approximately the same pattern transfer characteristic was obtained as in the case of using a photo mask (hereinafter referred to merely as the photo mask) formed on a mask substrate by the use, as a light shielding pattern, of

a metal film such as, e.g., chromium (Cr). The resist pattern 4 could be formed with a depth of field in which for example, at $0.19\text{ }\mu\text{m}$, and a line-and-space of $0.19\text{ }\mu\text{m}$ could be formed with a focal depth of $0.4\text{ }\mu\text{m}$.

Fig. 5 shows an example of the reduction projection exposure system used for this exposure treatment. The exposure light emitted from a light source 5a of the reduction projection exposure system 5 irradiates the photo mask 1PA1 through a fly's eyes lens 5b, irradiation shape adjusting aperture 5c, a condenser lenses 5d1, 5d2 and a mirror 5e. This photo mask 1PA1 is placed in the state in which the major surface (first major surface) on which the light shielding pattern is formed is directed downward (toward the semiconductor wafer 3 side). Therefore, the above-mentioned exposure light is irradiated from the back surface (second major surface) side of the photo mask 1PA1. By so doing, the mask pattern written on the photo mask 1PA1 is projected through a projection lens 5f onto the semiconductor wafer 3 which is a sample substrate. On the first major surface of the photo mask 1PA1, a pellicle 1p for preventing a defective transfer of the pattern due to the attachment of foreign matters is provided in some

cases. The photo mask 1PA1 is vacuum-sucked onto a mask stage 5h controlled by a mask position control means 5g, and aligned by a position detecting means 5i, whereby the center of the photo mask 1PA1 and the optical axis of the projection lens 5f are accurately aligned. The semiconductor wafer 3 is vacuum-sucked onto a sample stand 5j. The sample stand 5j is placed on a Z stage 5k which is movable in the direction of the optical axis of the projection lens 5f, that is, in the Z-axis direction, and the Z stage 5k is placed on an XY stage 5m. The Z stage 5k and the XY stage 5m are driven by respective driving means 5p1, 5p2 in response to control commands from a main control system 5n and can therefore be moved to a desired exposure position. The position is accurately monitored, by a laser precision-distance meter 5r, as the position of a mirror 5q fixed to the z stage 5k. Further, as the position detecting means 5i, an ordinary halogen lamp for example is used. In other words, it is not necessary to use any special light source for the position detecting means 5i (it is not necessary to introduce any novel technique or difficult technique anew), but a known reduction projection exposure system can be used. Therefore, The costs of the products manufactured by the use of

the photo mask 1PA1 on which the light shielding pattern is formed of a resist film are not increased.

Next, the case where the technical concept of the present invention is applied to the process of manufacturing a semiconductor integrated circuit device which has, for example, a twin well type CMIS (Complimentary MIS) circuit will be described by the use of Figs. 6 to 9.

Fig. 6 is a sectional view of the essential part of the semiconductor wafer 3 during a step for the manufacture thereof. The semiconductor wafer 3 comprises, for example, a plane and approximately circular semiconductor thin-plate. A semiconductor substrate 3s constituting the semiconductor wafer 3 comprises for example n-type Si single-crystal, and, above the semiconductor wafer 3, for example an n-well 6n and p-well 6p are formed. In the n-well 6n, for example phosphorus or As, which is an n-type impurity, is introduced. Further, in the p-well 6p, for example boron, which is a p-type impurity, is introduced.

On a major surface (first major surface) of this semiconductor substrate 3s, an isolating field oxide film 7 is formed by the LOCOS (Local Oxidization of Silicon) method or the like. The isolating portion may be formed in a groove shape. In other words, by

burying an insulator film into a groove dug in the thickness direction of the semiconductor substrate 3s, the isolating portion may be formed.

In an active region surrounded by this field oxide film 7, an nMISQn and a pMISQp are formed. The gate oxide films 8 of the nMISQn and pMISQp each comprises for example a silicon oxide film, which is formed by the thermal oxidation method or the like. Further, the gate electrodes 9 of the nMISQn and the pMISQp are each formed in such a manner that a gate forming film comprising, for example, low-resistance polycrystalline silicon is deposited by the CVD method or the like, and then, the thus deposited film is formed by the photolithography technique using the above-mentioned reduction projection exposure system 5 and the photo mask 1PA1 and the ordinary etching technique. Though not particularly so limited, the gate length is, for example, about 0.18 μm . A semiconductor region 10 of the nMISQn is formed in a self-aligning manner with respect to the gate electrode 9, by introducing, for example, phosphorus or arsenic into the semiconductor substrate 3S by the ion implantation method or the like using the electrode 9 as a mask. Further, a semiconductor region 11 of the pMISQp is formed in a self-aligning

manner with respect to the gate electrode 9 by introducing for example boron into the semiconductor substrate 3s by the ion implantation method or the like using the gate electrode 9 as a mask. However, the gate electrode 9 is not limited to the formation of, e.g., a single substance film of low-resistance polycrystalline silicon, but the formation of the gate electrode 9 is variously modifiable; for example, there may be employed a so-called polycide structure obtained in such a manner that a silicide layer such as, e.g., tungsten silicide or cobalt silicide is provided on a low-resistance polycrystalline silicon film; or there can also be employed a so-called polymetal structure obtained in such a manner that a metal film such as, e.g., tungsten is provided on a low-resistance polycrystalline silicon film through a barrier conductor film such as, e.g., titanium nitride or tungsten nitride.

First, on such semiconductor substrate 3s, an interlayer dielectric film 12 comprising for example a silicon oxide film is deposited by the CVD method or the like as shown in Fig. 7, and then, on the upper surface of the interlayer dielectric film 12, a polycrystalline silicon film is deposited by the CVD method or the like. Subsequently, the polycrystalline

silicon film is patterned by the photolithography technique using the above-mentioned reduction projection exposure system 5 and the photo mask 1PA1 and the ordinary etching technique, and thereafter, an
5 impurity is introduced into a predetermined region of the polycrystalline silicon film thus patterned, whereby wirings 13L and a resistor 13R are formed. After this, as shown in Fig. 8, on the semiconductor substrate 3s, an SOG (Spin On Glass) film 14
10 comprising for example a silicon oxide film is deposited by the coating method or the like; and then, in the interlayer dielectric film 12 and the SOG film 14, connecting holes 15 are bored so as to expose portions of the semiconductor regions 10, 11 and the
15 wiring 13L, by the photolithography technique using the above-mentioned reduction projection exposure system 5 and the photo mask 1PA1. Further, after a metal film comprising for example aluminum (AL) or an AL alloy is deposited by the sputtering method, this
20 metal film is patterned by the photolithography technique and the ordinary etching technique using the reduction projection exposure system 5 and the photo mask 1PA1 and the ordinary etching technique, whereby a first layer wiring 16L1 is formed as shown in Fig.
25 9. After this, a second layer wiring is formed in the

same manner as in case of forming the first layer wiring 16L1, thus manufacturing a semiconductor integrated circuit.

Thus, according to this Embodiment 1, for
5 example the following effects can be obtained:

(1). The light shielding pattern 1b and the mark pattern 1mr on the photo mask 1PA1 are constituted of a resist film, whereby the metal film etching step for forming the light shielding pattern and the step of
10 removing the resist film used as a etching mask used for the metal film etching can be deleted. Due to this, the manufacturing costs of the photo mask 1 can be reduced. Further, the accuracy of the pattern dimensions on the photo mask 1PA1 can be enhanced.
15 Further, the defects on the photo mask 1PA1 can be decreased.

(2). Since the various patterns comprising a resist film are not provided in that region of the outer periphery of the photo mask 1PA1 with which the
20 mounting portion 2 of the inspection equipment or the aligner is contacted, it becomes possible to prevent the occurrence of foreign matters due to the peeling-off or shaving-off of the above-mentioned resist film on the photo mask 1PA1 when the photo mask 1PA1 is
25 mounted onto the inspection equipment on the aligner

doe to mechanical shocks.

(3). Due to foregoing Item (2), the deterioration in the inspection accuracy and the deterioration in the transfer accuracy of the exposure patterns due to the peeling-off and shaving-off of the photo mask 1PA1 can be prevented.

(4). Due to foregoing Item (2), it becomes possible to present the occurrence of short-circuit defects and open-circuit defects between the patterns on the semiconductor wafer 3 due to the peeling-off and the shaving-off of the resist film on the photo mask 1PA1.

(5). Due to foregoing Items (1) to (4), it becomes possible to enhance the reliability of the semiconductor integrated circuit device.

(6). Due to foregoing Items (2) to (4), the manufacturing yield of the semiconductor integrated circuit devices can be enhanced.

Embodiment 2:

This Embodiment 2 is identical with foregoing Embodiment 1 except that the method of manufacturing the photo mask 1PA1 differs from that of Embodiment 1.

In case of manufacturing the above-mentioned ordinary photo mask, when the resist pattern used as

an etching mask for patterning the metal film for forming the light shielding pattern is formed by an electron beam writer or the like, the static electrification by the electrons produced at the time of performing electron beam writing can be prevented by which the metal film for forming the light shielding pattern is electrically connected to the earth. Accordingly, it is not necessary to perform electrification preventing treatment.

However, in case of manufacturing the above-mentioned photo mask 1PA1 according to the present invention, when a pattern is formed on the resist film 1R by the use of an electron beam writer for forming the light shielding pattern, the electrons irradiated are cut off from escape since the mask substrate 1a and the resist film 1R are alike insulators; and thus, they are charged to adversely affect the formation of the resist pattern (i.e., the light shielding pattern).

Thus, according to this Embodiment 2, the photo mask is manufactured in the following manner for example:

First, as shown in Fig. 10A, a transparent conductive film 17 is deposited on the mask substrate 1a. As the transparent conductive film 17, an ITO

(indium - tin oxide) film can be used for example.

This transparent conductive film 17 need not be processed. The reference numeral 18 denotes the

earth. Subsequently, as shown in Fig. 10B, on this

5 transparent conductive film 17, the above-mentioned resist film 1R is provided by coating as in case of foregoing Embodiment 1. the transparent conductive film 17 is electrically connected to the earth 18.

After this, as shown in Fig. 10C, predetermined

10 patterns (the light shielding pattern 1b and the mask pattern 1mr) are written on the resist film 1R by the use of the electron beam writer. In this case,

according to this Embodiment 2, the electrons irradiated to the mask substrate 1a are allowed to

15 escape to the earth 18 through the transparent conductive film 17. As a result, it becomes possible to suppress inconveniences such as the deterioration in shape of the resist pattern and the positional shift due to the static electrification by the

20 electrons. In this way, the photo mask 1PA2 is manufactured.

Further, the following method may alternatively be adopted. First, after the mask substrate 1a is prepared as shown in Fig. 11A, the resist film 1R is

25 provided by coating, as shown in Fig. 11B, on a major

surface of the mask substrate 1a as in case of foregoing Embodiment 1. Subsequently, according to this Embodiment 2, a water-soluble conductive organic film 19 is coated on the resist film 1R. As the water-soluble conductive organic film 19, for example ESPACER (manufactured by Showa Denko K.K.) AQUASAVE (manufactured by Mitsubishi Rayon Co., Ltd.) or the like was used. After this, in the state in which the water-soluble conductive organic film 19 is electrically connected to the earth 18, the above-mentioned electron beam writing treatment was carried out. After this, at the time of developing the resist film, the water-soluble conductive organic film 19 was removed. By the above-mentioned method, the static electrification by the electron beam could be prevented, and inconveniences such as the abnormality in shape of the patterns and the positional shift of the patterns could be prevented. The photo mask 1PA3 is manufactured in this way.

Embodiment 3:

In this Embodiment 3, a light screening region constituted of a metal film is provided in the vicinity of the outer periphery of a mask substrate constituting a photo mask, and openings are provided

in the light screening region, whereby an information
detecting pattern for reading the information of the
photo mask concerning, e.g., the above-mentioned
aligning mark, the calibrating mark, etc. Except for
5 this point, Embodiment 3 is identical with foregoing
Embodiments 1, 2.

Fig. 12 shows a concrete example of the photo
mask according to this Embodiment 3. Fig. 12A is a
plan view of the photo mask, Fig. 12B is a sectional
10 view taken along the line A-A, and Fig. 12C is a
sectional view of the photo mask, showing the state in
which the photo mask shown in Fig. 12A and Fig. 12B is
mounted on a predetermined apparatus.

In this Embodiment 3, a light shielding pattern
15 (light screening metal region) 1c is formed in the
vicinity of the outer periphery of a major surface of
a mask substrate 1a constituting a photo mask 1PA4.
This light shielding pattern 1c comprises a metal film
such as, e.g., chromium (Cr) and is formed in a plane
20 frame shape with a width, along the vicinity of the
outer periphery of the mask substrate 1a so as to
surround the above-mentioned integrated circuit
pattern region of the mask substrate 1a. The region
in which this light shielding pattern 1c is formed
25 corresponds to the peripheral region, i.e., the inner

peripheral region and the outer peripheral region, of the integrated circuit pattern of the above-mentioned photo mask 1PA1.

By the way, in this Embodiment 3, a mark pattern
5 lma which has the same function as the above-mentioned mark pattern 1mr is formed in a portion of this light shielding pattern 1c. Here, however, the mark pattern lma is formed by light transmitting regions bored in portions of the light shielding pattern 1c. More
10 specifically, the mark pattern lma is formed in such a manner that portions of the metal film constituting the light shielding pattern 1c are removed to expose the transparent mask substrate 1a lying beneath. Accordingly, in this Embodiment 3, in case the aligner
15 described in connection with Fig. 5 is used, in other words, in case that such an aligner as uses an ordinary halogen lamp or the like for the position detection of the photo mask is used, the contrast of the light which has transmitted through the mark
20 pattern lma can be sufficiently obtained, so that the recognizing ability of the mark pattern lma can be enhanced. Due to this, the relative alignment between the photo mask 1PA4 and the aligner can be carried out with ease and yet with high accuracy. According to
25 the result of the examination made by the present

inventor, alignment equal to that of the above-mentioned ordinary photo mask has become possible.

Further, in this Embodiment 3, as shown in Fig. 12C, the mounting portion 2 of the inspection equipment or the aligner is directly contacted with the light shielding pattern 1c. However, since a resist film is not formed on the light shielding pattern 1c, the occurrence of foreign matters due to the peeling-off and the shaving-off of the resist film is not brought about even if the photo mask 1PA4 is mounted on the inspection equipment or the aligner. Further, the chromium or the like constituting the light shielding pattern 1c is hard, so that the occurrence of foreign matters due to the peeling-off or shaving-off of the chromium or the like is not caused, either. Therefore, the same effect as the effect described in connection with foregoing Embodiment 1 can be obtained.

Also in this Embodiment 3, a light shielding pattern 1a constituted of a resist film 1R is likewise disposed in the integrated circuit pattern region in the center of the mask substrate 1a, as in the cases of foregoing Embodiments 1, 2.

Next, an example of the flow of a series of manufacturing steps for the manufacture of the photo

mask 1PA4 according to this Embodiment 3 will be described.

The ordinary photo mask manufacturing step can be divided into the step of manufacturing a substrate (mask blanks) on which the light screening film made of chromium or a semitransparent film to be described later is formed on a whole major surface of the mask substrate and the photo mask manufacturing step for forming a semiconductor integrated circuit forming pattern on the mask blanks. The substrate and the photo mask are manufactured in different work sections or sites in some cases.

The photo mask manufacturing step according to this Embodiment 3 is divided into a mask blanks manufacturing step, a common light shielding pattern forming step for forming, in the outer peripheral portion of the mask substrate, a pattern used in common by various projection aligners, and a resist pattern forming step. The respective steps are carried out in different work sites or in different manufacturing companies in some cases.

For example, Fig. 13A shows the above-mentioned common light shielding pattern manufacturing step. As for the common pattern, various common patterns can be prepared in accordance with the respective

semiconductor integrated circuits manufactured or the projection aligners used for the exposure treatment.

First, after the common light shielding pattern (corresponding to the light shielding pattern 1c shown

5 in Fig. 12) (Step 100), the absence or presence of defects is inspected (Step 101). Here, in case that no defect is found, the common light shielding pattern is stocked as a completed photo mask at the common light shielding pattern forming stage (Step 102). On
10 the other hand, in case that some defects exist, correction or the like is made (Step 103), and the common light shielding pattern is stocked after the correction (Step 102).

As stated above, in the photo mask manufacture
15 according to this Embodiment 3, the mask substrate can be stocked during the photo mask manufacturing step, so that the manufacturing time and developing time of the semiconductor integrated circuit devices can be greatly shortened. In case of the ordinary photo
20 mask, the substrate cannot be stocked during an intermediate step for the mask substrate manufacture, so that the whole course ranging from the deposition of the light screening film (the mask blanks manufacturing step) to the patterning of predetermined
25 patterns must be continuously carried out, while,

according to this Embodiment 3, the photo masks
processed as far as the common light shielding pattern
manufacturing step can be stocked. Due to this, in
case of manufacturing or developing a semiconductor
5 integrated circuit apparatus, at the time of forming
the concrete mask patterns for a semiconductor
integrated circuit pattern, the manufacture of the
photo mask can be started from the stage where the
photo mask was stocked, so that the photo mask
10 manufacturing time can be shortened. Due to this, the
step of forming the semiconductor integrated circuit
pattern can be terminated in a shorter time.
Therefore, the technical concept of the present
invention is particularly suited to the manufacture of
15 a photo masks for logic devices which are high in the
frequency of developing product types.

Further, in case of the photo mask 1PA4 at the
stage shown in Fig. 13A, the light screening portion
is mainly the outer peripheral portion of the mask
20 substrate, so that a metal film such as a chromium
(Cr) film may not be provided in the central portion
of the substrate (mask blanks) in which a light
screening film or a semitransparent film is formed
over the whole major surface of the mask substrate or
25 in the portion in which an element pattern is

scheduled to be formed (that is, in the above-mentioned integrated circuit pattern region). Or even if the metal film exists, defects such as pinholes etc. do not matter, so that the quality management of the mask blanks can be alleviated, and thus, the yield of the mask blanks can be greatly enhanced.

Subsequently, Fig. 13B shows the manufacturing step for forming a resist pattern. First, the mask blanks on which the common light shielding pattern is formed is used; and, in the integrated circuit pattern region, the resist film is subjected to exposure, development and hardening treatment, whereby a device manufacturing resist pattern (corresponding to the light shielding pattern 1b shown in Fig. 12) (Step 104). Subsequently, inspections such as a defect inspection and a dimensional inspection are carried out to the mask substrate (Step 105). In case the inspected product has passed these inspections, the completion of a photo mask follows (Step 106). However, As a result of these inspections, the resist film of the photo masks which have failed to pass the inspections and thus are below the standards are removed (Step 107), which are put to reuse. As stated above, in this Embodiment 3, the mask blanks with common light shielding patterns can be reused. In

other words, in case the light shielding pattern for the manufacture of devices is formed of a metal film, it is difficult to remove it for reuse, in view of securing the quality of the photo mask. However, to
5 remove and reuse the resist film as according to this Embodiment 3 does not take much time, and further, it can be easily done without lowering the quality of the photo mask. Thus, it follows that the effective utilization of resources becomes possible.

10 Next, an example of the concrete manufacturing method will be described concerning each step of the above-mentioned photo mask manufacturing steps.

 First, as shown in Fig. 14A, a metal film with high light screening properties such as, e.g., a
15 chromium film is deposited on a major surface of a mask substrate 1a, and thereafter, this is patterned by the photolithography technique and the etching technique, whereby the above-mentioned light shielding pattern 1c and the mark pattern 1ma are formed on the
20 major surface of the mask substrate 1a. In the integrated circuit pattern region in the central portion of the mask substrate 1a, the light shielding pattern 1c is not formed, an opening is bored, and thus, the transparent mask substrate 1a is exposed.
25 The steps as far as this step correspond to the

manufacturing steps shown in Fig. 13A.

Next, as shown in Fig. 14B, on the major surface of the mask substrate 1a on which the step of forming the common light shielding pattern is completed, the
5 above-mentioned resist film 1R is coated so as to cover the light shielding pattern 1c, and thereafter, the above-mentioned water-soluble conductive organic film 19 is applied on the resist film 1R thus coated. Subsequently, as in case of the foregoing Embodiment
10 2, the above-mentioned electron beam writing treatment was carried in the integrated circuit pattern region of the mask substrate 1a, in order to form a light shielding pattern for the semiconductor integrated circuit pattern, in the state in which the water-
15 soluble conductive film 19 is electrically connected to the earth 18. After this, the resist film 1R was subjected to a developing treatment, the water-soluble conductive organic film 19 was removed, and thus, as shown in Fig. 12, a light shielding pattern 1b
20 comprising a resist film was formed in the integrated circuit pattern region of the mask substrate 1a. The steps as far as this step correspond to the manufacturing steps shown in Fig. 13B.

According to such Embodiment 3, the following
25 effects can be obtained in addition to the effects

obtained by the foregoing Embodiments 1, 2:

(1). Since the light shielding pattern 1c is provided in the outer periphery of the mask substrate 1a of the photo mask 1PA4, and, by removing a portion thereof, the mark pattern 1ma is formed, the accuracy in detection of the mark pattern can be enhanced. Accordingly, the ability of detecting the information of the photo mask 1PA4 can be enhanced

(2). Due to foregoing Item (1), the accuracy in detection of the calibrating mark of the photo mask 1PA4 can be enhanced in case of inspecting the photo mask 1PA4, so that it is possible to enhance the inspection accuracy of the photo mask 1PA4. Therefore, the reliability of the photo mask 1 can be enhanced.

(3). Due to foregoing Item (1), the accuracy in alignment between the photo mask 1PA4 and the aligner can be enhanced. Therefore, the accuracy in the transfer of the patterns onto the semiconductor wafer and the alignment accuracy can be enhanced.

(4). Due to foregoing Items (1), (2), (3), the reliability and manufacturing yield of the semiconductor integrated circuit devices manufactured by the use of the photo mask 1PA4 can be enhanced.

(5). The mask blanks with the common light

shielding pattern can be reused. In other words, the effective utilization of resources becomes possible.

(6). The quality management of the mask blanks in the photo mask manufacturing steps can be
5 alleviated, and thus, the yield of the mask blanks can be greatly enhanced.

(7). Due to foregoing Items (5) and (6), the costs of the photo mask 1PA4 can be decreased, so that the costs of the semiconductor integrated circuit
10 device can be decreased.

(8). The mask substrate 1a can be stocked during the steps of manufacturing the photo mask 1PA4, so that the length of time required for the manufacture and development of semiconductor integrated circuit
15 devices can be greatly shortened.

Embodiment 4:

This embodiment 4 relates to an example of the case where a transparent thin-film pellicle which
20 functions to prevent foreign matters from attaching to the photo mask pattern forming surface (first major surface) is disposed on the major surface of the photo mask. This Embodiment 4 is identical with the foregoing Embodiments 1 to 3 except for the above-
25 mentioned point. Here, description will be made with

reference to the use of the photo mask constituted in such a manner that a light shielding pattern comprising a metal film is provided in the vicinity of the outer periphery of the mask substrate as in case of the photo mask described, for example, in connection with foregoing Embodiment 3.

Fig. 15 shows a concrete example of the photo mask according to this Embodiment 4. Here, Fig. 15A is a plan view of the photo mask, and Fig. 15B is a sectional view of the photo mask taken along the line A-A in Fig. 15A showing the state in which the photo mask is mounted on a predetermined apparatus.

According to this Embodiment 4, a pellicle 1p is fixed in a state joined through a pellicle sticking frame 1pf to a major surface (first major surface) of a photo mask 1PA5. The pellicle is a structural body which has a transparent film and is provided over a predetermined distance from the major surface or the major and back surfaces of the mask substrate, in order to avoid foreign matters from attaching to the photo mask. This predetermined distance is designed by taking into consideration the foreign matters attaching to the protective film surface and the transferability of the foreign matters onto the semiconductor wafer. In this Embodiment 4, the

pellicle 1p is disposed in a pellicle cover region of a photo mask 1PA5. That is, the pellicle 1p is disposed so as to plane-wise overlap the whole of the above-mentioned integrated circuit pattern region of the photo mask 1PA5 and a portion of the light shielding pattern 1c of the above-mentioned inner peripheral region.

According to this Embodiment 4, the base portion of the pellicle sticking frame 1pf is joined and fixed in a state directly contacted with the light shielding pattern 1c in the above-mentioned inner peripheral region of the photo mask 1PA5. As a result, the pellicle sticking frame 1pf can be prevented from being peeled off. Further, if a resist film is formed at the position at which the pellicle sticking frame 1pf is mounted, then, when the pellicle 1p is mounted and removed, it becomes a cause for the peeling-off of the resist film and for the generation of foreign matters. In this Embodiment 4, the pellicle sticking frame 1pf is joined in a state directly contacted with the light shielding pattern 1c, so that the generation of such foreign matters can be prevented. Such an effect is obtained also by joining and fixing the pellicle stacking frame 1pf in a state directly contacted with the mask substrate 1a. Further, this

Embodiment 4 is also constituted in such a manner that, as shown in Fig. 15B, no resist film is formed in the portion in which the photo mask 1PA5 and the mounting portion 2 of the projection aligner are
5 contacted. As a result, the occurrence of foreign matters due to the peeling-off and shaving-off of the resist film can likewise be prevented as in the cases of foregoing Embodiments 1 to 3.

Further, in this Embodiment 4, a position
10 calibrating mark pattern 1mb is formed in the light shielding pattern 1c. This position calibrating mark pattern 1mb is a pattern for detecting the positional information of the photo mask 1 directly from the photo mask 1 itself when a predetermined pattern is
15 written on the photo mask 1 by the use of the electron beam writer. According to this Embodiment 4, when a predetermined integrated circuit pattern is pattern-formed in the integrated circuit pattern region of the mask substrate by the use of the electron beam writer,
20 the mask pattern 1mb in the mask substrate 1a is read out at a rate of one per several seconds, whereby pattern writing is carried out, correcting (adjusting) the position to be irradiated by the electron beam for writing the pattern during the pattern writing step.
25 As a result, the pattern writing position accuracy of

the electron beam writer can be enhanced.

The provision of such a mark pattern lmb is, for example, for the following reason: In case of an ordinary electron beam writer, the writing treatment to the photo mask is carried out in vacuum. As for the holding of the photo mask in vacuum, as symbolically shown in Fig. 16, the mask substrate 1a or a cassette 21 on which the mask substrate 1a is mounted is pushed to three pins 20a of a mask holding portion 20 on a moving stage of the electron beam writer; and thus, the mask substrate 1a or the cassette 21 is mechanically fixed by a push pin 20b. Here, in case of the ordinary electron beam writer, a position detecting mark pattern 20m mounted on the mask holding portion 20 is detected a plurality of times during the writing to thereby correct pattern writing the positional shift by the positional drift of the electron beam. The mask substrate 1a on the mask holding portion 20 (stage) is mechanically fixed as mentioned above, so that the relative positional relationship between the mark pattern 20m of the mask holding portion 20 and the mask substrate 1a should be constant, but, in actuality, by the shocks caused by the stage which moves at high speed, a slight positional deviation is caused between the mark

pattern 20m and the mask substrate 1a in some cases.
Due to this, in spite of the fact that the position of
the mask substrate 1a is read out from the mark
pattern 20m during the electron beam writing step, a
5 positional deviation is caused of the written pattern.

Thus, according to this Embodiment 4, the
position correcting mark pattern 1mb is disposed on
the photo mask 1PA5 (the mask substrate 1a) itself so
that the position thereof can be directly detected
10 from the mask substrate 1a itself. As a result, the
positional deviation including also the deviation in
the holding of the mask substrate 1a can be corrected,
so that the error in arrangement of the patterns can
be decreased. Such a mark pattern 1mb is constituted
15 depending on, e.g., whether the pattern position lies
in the light transmitting region or in the light
screening region; and information detection is
executed in accordance with the reflected state of a
position detecting beam or a detection light
20 irradiated there. As the position detecting means,
there can be used the type which uses the electron
beam of the electron beam writer, the type which uses
the laser beam by a laser lighter or other types.
Particularly, the application of a system or apparatus
25 having a high positional accuracy is desirable. This

mark pattern lmb can also be formed at the step of forming the common light shielding pattern in the above-mentioned photo mask manufacture, and it is also effective to form this mark pattern lmb at the above-mentioned mask blanks manufacturing step.

According to such Embodiment 4, the following effects can be obtained in addition to the effects obtained by foregoing Embodiment 3:

(1). Since the pellicle lp is provided on the photo mask lPA5, it is possible to prevent foreign matters from attaching to the photo mask lPA5, and it is also possible to suppress or prevent the deterioration of the transferred pattern due to the foreign matters.

(2). Since the pellicle sticking frame lp1 is joined in a state directly contacted with the light shielding pattern lc or the mask substrate la, it is possible to prevent the light-screening-pattern forming resist film from being peeled off or shaved off when the pellicle lp is mounted or removed. Due to this, it is possible to prevent the occurrence of foreign matters due to the peeling-off or shaving-off of the resist film.

(3). Since the electron beam writing position correcting mark pattern lmb is provided on the photo

mask 1PA5 itself, it becomes possible to enhance the positional accuracy in the pattern writing by the electron beam writer.

5 Embodiment 5:

 This Embodiment 5 relates to the case where the present invention is applied to a so-called phase shift mask which causes a difference between the phases of the exposure light rays transmitting through
10 the photo mask.

 This Embodiment 5 is identical with foregoing Embodiments 1 to 4 except for the above-mentioned point.

 Fig. 17A shows a sectional view of the essential
15 part of the phase shift mask. On a major surface (first major surface) of a mask substrate 1a constituting a phase shift mask 1PS1, a phase shift film 1d is formed so as to cover light shielding patterns 1b, 1c and the mask substrate 1a. The phase
20 shift film 1d may comprise, for example, a transparent SOG (Spin On Glass) film (Either an organic SOG film or an inorganic SOG film may be used. In case of an organic SOG film, however, the exposure light is absorbed, so that an optimum film thickness must be
25 set. From the optical viewpoint, the use of an

inorganic SOG film is preferable), and, at a predetermined position of the phase shift film 1d, a groove 1d1 with a predetermined depth is formed. The depth of this groove 1d1 is set to such a depth that the phase of the exposure light which has transmitted through the region in which the groove 1d is formed and the phase of the exposure light which has transmitted through the region in which the groove 1d1 is not formed are inverted with respect to each other. Fig. 17B shows the state in which the exposure light rays 22a, 22b irradiated from the back surface (second major surface) side of the mask substrate 1a of the phase shift mask 1PS1 are phase-inverted with respect to each other. The exposure light 22a passes through the relatively thick portion of the phase shift film 1d. On the other hand, the exposure light 22b passes through the portion in which the groove 1d1 is dug to such a depth that the phase of the exposure light 22b is inverted with respect to the phase of the exposure light 22a, so that the exposure light 22b is inverted in phase with respect to the exposure light 22a. More specifically, a phase difference of, e.g., 180° is caused. As a result, in the mutually adjacent transmitting portions, a phase shift effect is obtained; and thus, the resolution of the pattern

transferred onto the semiconductor wafer can be enhanced.

Further, in the phase shift mask 1PS1 according to this Embodiment 5, the phase shift film 1d covers the whole surface of the major surface of the mask substrate 1a. Thus, in case the phase shift mask 1PS1 is mounted on an inspection equipment or an aligner, the phase shift film 1d of the phase shift mask 1PS1 comes into contact with the mounting portion of the inspection equipment or the aligner. Accordingly, as in the cases of foregoing Embodiments 1 to 4, the mounting portion of the inspection equipment or the aligner is not directly contacted with the patterns (the light shielding pattern 1b, etc.) constituted of a resist film on the mask substrate 1a, so that the peeling-off or the shaving-off of the resist film due to the mounting of the phase shift mask 1PS1 can be prevented, and the occurrence of foreign matters due to the above-mentioned peeling-off or shaving-off can be prevented.

Next, an example of the method for the manufacture of the phase shift mask 1PS1 according to this Embodiment 5 will be described. First, as shown in Fig. 18A, the above-mentioned light shielding pattern 1b constituted of a resist film and the light

shielding pattern 1c constituted of a metal film are formed on the mask substrate 1a in the same manner as in the cases of foregoing Embodiments 3, 4.

Subsequently, as shown in Fig. 18b, on a major surface
5 (the first major surface) of the mask substrate 1a, the phase shift 1d comprising, e.g., an SOG film is deposited, and then, an electron beam resist film 23 is deposited on the thus deposited phase shift film 1d. After this, on this electron beam resist film 23,
10 a desired pattern is written by an electron beam writing treatment, and then, as shown in Fig. 18c, a resist pattern 23a constituted of the electron beam resist film is formed via an ordinary step.

Here, also, the above-mentioned static
15 electrification preventing treatment was adopted. After this, by the use of the resist pattern 23a as an etching mask, the phase shift film 1d exposed from the resist pattern 23a was removed by etching to form the groove 1d1. Thereafter, the resist pattern 23a was
20 removed, whereby the phase shift mask 1PS1 shown in Fig. 17 was obtained.

According to such Embodiment 5, it is possible to obtain, for example, the effect that the resolution of the patterns transferred onto the semiconductor
25 wafer, in addition to the effects obtained by

foregoing Embodiment 3.

Embodiment 6:

5 This Embodiment 6 relates to a modification of the phase shift mask according to foregoing Embodiment 5. Except for this point, Embodiment 6 is identical with foregoing Embodiments 1 to 5.

10 In this Embodiment 6, the phase shift film 1d is removed in the above-mentioned outer peripheral region of the mask substrate 1a constituting the phase shift mask 1PS2, and thus, the light shielding pattern 1c is exposed, as shown in Fig. 19A. Fig. 19B shows the state in which this phase shift mask 1PS2 is mounted on the aligner or the like, symbolically depicting how
15 the phase inversion between the exposure light rays 22a, 22b is effected when the exposure light rays are irradiated from the back surface side (the second major surface) of the phase shift mask 1PS2, wherein the mounting portion 2 is directly contacted with the
20 light shielding pattern 1c of the photo mask 1PS2. Therefore, in case of this Embodiment 6, the same effects as those of foregoing Embodiments 1 to 5 can be likewise obtained. The manufacture of this phase shift mask 1PS2 can be achieved in such a manner that,
25 after or before the step shown in Fig. 18B, a resist

pattern is formed so as to expose the outer peripheral region of the outer periphery of the major surface of the mask substrate 1a is exposed and yet cover the portions other than the above-mentioned outer peripheral region, and then, this resist pattern is used as an etching mask to etched off the phase shift film 1d exposed therefrom.

Embodiment 7:

10 This Embodiment 7 relates to the case where the present invention is applied to a semitransparent shift mask (the above-mentioned halftone mask). Except for this point, this Embodiment 7 is identical with foregoing Embodiments 1 to 6.

15 Fig. 20 shows an example of the halftone type phase shift mask 1PS3 according to this Embodiment 7. In the integrated circuit pattern region of this phase shift mask 1PS3, a halftone pattern (halftone light shielding pattern) 1e1 for transferring the

20 semiconductor integrated circuit pattern is formed. This halftone pattern 1e1 is constituted of a resist film which has been described in connection with foregoing Embodiment 1, etc., but this halftone pattern 1e1 is semitransparent with respect to the

25 exposure light, and the film thickness thereof is

adjusted to the value which inverts the phase of the exposure light. Fig. 20B shows how the phase inversion of the exposure light rays 22a, 22b which have been irradiated from the back surface (second major surface) side of the phase shift mask 1PS3 according to this Embodiment 7 is effected. The exposure light 22a which has passed through the halftone pattern 1e1 is inverted in phase with respect to the exposure light 22b which has passed through the transparent portion. In other words, the phases of these exposure light rays 22a, 22b deviate by 180° from each other. Further, the transmissivity of the halftone pattern 1e1 is such that the light intensity of the exposure light 22a which has transmitted through the halftone pattern 1e1 is about 2 to 10% with respect to the exposure light 22a before its transmission through the halftone pattern 1e1. Therefore, the halftone pattern 1e1 serves substantially as a light screening portion and yet has the effect of making the boundary portion of the transferred patterns clear and sharp. The method of patterning the halftone pattern 1e1 is the same as the patterning method of the light shielding pattern 1b according to foregoing Embodiments 1 to 6.

In case of the phase shift mask for ArF, the

absorption of the resist film constituting the mask is large, so that, in order to realize both the transmissivity of about 2 to 10% as mentioned above and phase inversion at the same time, adjustment must
5 be made of the resist film for forming the halftone pattern 1e1. On the other hand, in case of the phase shift mask for an F₂ laser beam with a wavelength of 163 nm, the absorption by the resist film is small, so that this phase shift mask is favorable in realizing
10 the above-mentioned transmissivity of about 2 to 10% and phase inversion at the same time.

By such Embodiment 7, the effects obtained by foregoing Embodiments 1 to 6 can also be obtained.

15 Embodiment 8:

This Embodiment 8 relates to a modification of the halftone type phase shift mask according to foregoing Embodiment 7. Except for this point, Embodiment 8 is identical with foregoing Embodiments 1
20 to 7.

In this Embodiment 8, the phase difference is set depending on the film thickness of the halftone pattern, so that it is necessary to bring the thickness into a predetermined range. Due to this, it
25 becomes difficult to set the intensity of the light

passing through the halftone pattern in some cases.

Thus, according to this Embodiment 8, the above-mentioned phase difference is not set only by the film thickness of the halftone pattern, but the phase difference is set by adjusting the film thickness and the depth of grooves dug in the mask substrate (that is, the thickness of the mask substrate in the groove-formed portions). As a result, according to this Embodiment 8, the effect that the intensity setting of the light which transmits through the halftone pattern can be facilitated, is obtained in addition to the effects obtained by foregoing Embodiments 1 to 7. Further, the range of materials for forming the halftone pattern can be increased.

Fig. 21A shows a concrete example of the halftone type phase shift mask 1PS4. In this halftone type phase shift mask 1PS4, the halftone pattern 1e2 was rendered into a thin film and semitransparent; and thus, phase inversion was realized by the thickness of the halftone pattern 1e2 and the thickness of the mask substrate 1a in the portions of the grooves 1g formed in the mask substrate 1a. The halftone pattern 1e2 was formed by the use of a novolac series resin with a thickness of, e.g., about 50 nm. As a result, the transmissivity of the halftone pattern 1e2 became 5%.

However, this transmissivity is limited to 5% but can be variously altered; in a range of, e.g., about 2 to 20%, selection satisfying the purpose can be made.

The phase inversion in this case was about 90°. Due to

5 this, grooves 1f with a depth of about 90 nm were dug in the mask substrate 1a so that the exposure light which has transmitted through the photo mask 1PS4 could obtain a phase inversion of about 180° in total. The film thickness of the halftone pattern 1e2 is not
10 limited to this value but can be variously altered; the film thickness may be adjusted so that the phase may be inverted in accordance with the refractive index of the material, the exposure light wavelength, etc.

15 This phase shift mask 1PS4 is formed in the following manner for example: First, as in case foregoing Embodiment 7, etc., the light shielding pattern 1c and the halftone pattern 1e2 are formed on the mask substrate 1a as shown in Fig. 21B, and
20 thereafter, by the use as etching mask of the light shielding pattern 1c and the halftone pattern 1e2, the portions of the mask substrate 1a which are exposed from there are selectively etched off by an amount corresponding to a predetermined depth. By so doing,
25 the grooves 1f shown in Fig. 21A are formed in a self-

aligning manner with respect to the halftone pattern
le2, and thus, the photo mask 1PS4 is manufactured.
According to this Embodiment 8, the halftone type
phase shift mask 1PS4 with a transmissivity of, e.g.,
5 5% could be manufactured. In case of the example
shown in Fig. 21A, the portion of the mask substrate
1a which lies in the mark pattern 1ma region is also
removed by etching and dug in at the time of forming
the grooves 1f, in order to simplify the mask
10 manufacturing step, but it is also possible not to
remove by etching the portion of the mask substrate 1a
lying in this region.

Embodiment 9:

15 This Embodiment 9 relates to a modification of
the halftone type phase shift mask according to
foregoing Embodiments 7, 8. In this Embodiment 9, in
order to give a solution to the problem described in
connection with foregoing Embodiment 8, the phase of
20 the above-mentioned exposure light is adjusted not
only by the halftone pattern but by providing a
different film which plane-wise overlaps the halftone
pattern. By this measure, according to Embodiment 9,
the effect that the intensity setting of the light
25 transmitting through the halftone pattern can be

facilitated as in case of foregoing Embodiment 8, can be obtained, in addition to the effects obtained by foregoing Embodiments 1 to 7. Further, the range of materials for forming the halftone pattern can be increased.

Fig. 22A shows a concrete example of the halftone type phase shift mask according to Embodiment 9. In this halftone type phase shift mask 1PS5, between a halftone pattern 1e3 similar to that of foregoing Embodiment 8 and a mask substrate 1a, a transparent phase adjusting film 1g comprising, e.g., a silicon oxide film is provided, so that, by adjusting the film thickness of the halftone pattern 1e3 and the film thickness of the phase adjusting film 1g, the above-mentioned phase inversion is realized.

This phase shift mask 1PS5 is formed, for example, in the following manner: First, as shown in Fig. 22B, on a major surface (first major surface) of the mask substrate 1a, the phase adjusting film 1g comprising, e.g., a silicon oxide film is formed by the sputtering method, the CVD method (Chemical Vapor Deposition) method or the coating method, and thereafter, on the phase adjusting film 1g thus formed, a light shielding pattern 1c and the halftone pattern 1e3 are formed as in the cases of foregoing

Embodiments 7, 8, etc. Subsequently, only with the above-mentioned halftone pattern 1e3, the phase inversion obtained was about 90° , so that the phase adjusting film 1g lying beneath the halftone pattern 1e3 and the light shielding pattern 1c was dug by, e.g., about 90 nm by the use of the halftone pattern 1e3 and the light shielding pattern 1c as an etching mask, whereby a phase inversion of about 180° in total was obtained. In this way, the halftone mask 1PS5 shown in Fig. 22A is manufactured. According to this Embodiment 9, likewise, a halftone type phase shift mask 1PS5 with a transmissivity of, e.g., 5% could be manufactured. The film thickness of the halftone pattern 1e3 is not limited to this value as in case of foregoing Embodiment 8. Further, also in this Embodiment 9, in order to simplify the mask manufacturing step, the phase adjusting film 1g portion in the mark pattern 1ma region is also removed by etching at the time of patterning the phase adjusting film 1g, but it is also possible not to etch off the portion of the phase adjusting film 1g which lies in this region.

Embodiment 10:

This Embodiment 10 relates to a modification of

the halftone type phase shift mask according to foregoing Embodiments 7, 8, 9 and a modification of the method for the manufacture of the above-mentioned halftone type phase shift mask. Except for the above-mentioned point, this Embodiment 9 is identical with foregoing Embodiments 1 to 9.

In this Embodiment 10, likewise, the constitution for giving a solution to the problem described in connection with foregoing Embodiment 8. As a result, this Embodiment 10 can obtain the effect that the intensity setting of the light which transmits through the halftone pattern can be facilitated, is obtained as in the cases of foregoing Embodiments 8, 9, in addition to the effects obtained by foregoing Embodiments 1 to 7. Further, the range of materials selected for forming the halftone pattern can be increased.

An example of the method for the manufacture of the halftone type phase shift mask according to this Embodiment 10 will now be described by referring to Fig. 23.

First, as shown in Fig. 23A, on a major surface (first major surface) of a mask substrate 1a, a light shielding pattern 1c and a mark pattern 1ma as mentioned above are formed as in the cases of foregoing

Embodiments 1 to 9. In other words, the above-mentioned common light shielding pattern forming step is carried out. Subsequently, as shown in Fig. 23B, on the major surface of the mask substrate 1a, a resist mask 24 which is transparent to the exposure light is formed by coating so as to cover the above-mentioned light shielding pattern 1c and the above-mentioned mask substrate 1a, and further, on the thus provided resist film 24, a resist film 25 with light screening properties as used in foregoing Embodiment 7 was formed of a thin film and made semitransparent. Here, as the transparent resist film 24, a PGMA 24 (polyglycidyl methacrylate) or the like which is, e.g., of the positive type was used. Further, the resist film 25 with light screening properties was formed by the use of a novolac series resin which has a thickness of about 50 nm and is, e.g., of the negative type. After this, on the resist film 25, a desired integrated circuit pattern was written by the use of an electron beam 26 or the like. Here, also, a static electrification preventing treatment was conducted. After this, an ordinary developing treatment was conducted to develop the resist film 25, whereby a halftone pattern 1e4 is formed as shown in Fig. 23C.

Subsequently, the major surface of the mask substrate 1a was subjected to an ordinary exposure treatment to expose the portion of the resist film 24 which is exposed from the halftone pattern 1e4 having light screening properties, and thereafter, a developing treatment is performed whereby, as shown in Fig. 23D, beneath the halftone pattern 1e4, a phase adjusting film 1g constituted of the resist film 24 and in a self-aligning manner with respect to the halftone pattern 1e4 so as to plane-wise overlap the halftone pattern 1e4. In this way, a phase shift mask 1PS6 was manufactured. In the structure of this phase shift mask 1PS6, the phase adjusting film 1g is provided only beneath the halftone pattern 1e4. The phase adjustment of the exposure light which transmits through the phase shift mask 1PS6 is made through the film thickness of the halftone pattern 1e4 and the film thickness of the phase adjusting film 1g. As a result, phase inversion could be realized between the light which has transmitted through the stacked pattern region consisting of the halftone pattern 1e4 and the phase adjusting film 1g and the light which has transmitted through the mask substrate 1a. Further, the transmissivity of the stacked pattern region turned out to be about 5%. Thus, the halftone

type phase shift mask 1PS6 with a transmissivity of about 5% could be fabricated as in the cases of foregoing Embodiments 8, 9, etc.

5 Embodiment 11:

 This Embodiment 11 relates to a modification of foregoing Embodiment 1.

 Through the result of the examination made by the present inventor, the following has been found:

10 It is also effective that, after, on the major surface of the mask substrate, the light shielding pattern for forming the integrated circuit pattern and the mark pattern is formed of the above-mentioned resist film, and thereafter, on the above-mentioned major surface,
15 a transparent protective film is formed so as to cover the light shielding pattern. By this measure, the mechanical strength of the light shielding pattern formed of the above-mentioned resist film can be enhanced. Further, by shutting off the oxygen by the
20 protective film, the change in the film quality of the light shielding pattern formed of the resist film can be prevented.

 Fig. 24 shows a concrete example of this Embodiment 11. Over the whole of a major surface
25 (first major surface) of a mask substrate 1a

constituting the photo mask 1PA6, a protective film 1h comprising, e.g., a silicon oxide film or a silicon compound coating. In case the protective film 1h was comprised of a silicon oxide film or the like, the protective film 1h was formed by, e.g., the sputtering method or the CVD method. Further, in case the protective film 1h was comprised of a silicon compound coating, it was subjected to heat treatment at about 100 to 200° C after the coating thereof.

Further, in the photo mask 1PA6 according to this Embodiment 11, the protective film 1h covers the whole major surface of the mask substrate 1a. Thus, in case of mounting the photo mask 1PA6 on the inspection equipment, the aligner or the like, the protective film 1h of the photo mask 1PA6 is contacted with the mounting portion of the inspection equipment, the aligner or the like. Therefore, as in the cases of foregoing Embodiments 1 to 9, the mounting portion of the inspection equipment, the aligner or the like is not directly contacted with the pattern (the light shielding pattern 1b, etc.) constituted of a resist film on the mask substrate 1a, so that the peeling-off or shaving-off of the resist film due to the above-mentioned mounting can be prevented, and the occurrence of foreign matters due to the peeling-off

or shaving-off can also be prevented. This structure can be also applied to the photo masks according to foregoing Embodiments 2 to 4.

5 In the above, the invention achieved by the present inventor has been concretely described on the basis of its embodiments, but it is a matter of course that the invention is not limited to the foregoing embodiments but can be variously modified without departure from the gist of the invention.

10 For example, foregoing Embodiments 1 to 10 have been described with reference to the case where the wiring is of the ordinary wiring structure, but the invention is limited to this, but the wiring may alternatively be formed by, e.g., the so-called
15 damascene method or the dual damascene method according to which a wiring is formed in an insulator film or a wiring is formed by burying a conductor film into a groove for a hole.

Further, foregoing Embodiments 1 to 10 have been
20 described with reference to the case where a semiconductor substrate comprising an elemental semiconductor is used, but the invention is not limited to such case, but, for example, an SOI (Silicon On Insulator) substrate constituted by
25 providing a thin semiconductor layer on an insulator

layer, or an epitaxial substrate comprising an epitaxial layer provided on a semiconductor substrate.

In case that the mark pattern is formed of a resist film in foregoing Embodiments 1, 11, an absorbing material which absorbs the mark detecting light (such as, e.g., the probe light of a defect inspection equipment (the probe light being light which has a wavelength, of, e.g., 500 nm, greater than the exposure wavelength)) may be added to the resist film.

In the above, the invention achieved by the present inventor has been described, mainly, with reference to the case where the invention is applied to the method for the manufacture of a semiconductor integrated circuit device with a CMOS circuit which belongs to the field of utilization constituting the background of the invention, but the invention is not limited to this, but can also be applied to a semiconductor integrated circuit device with a memory circuit such as, e.g., a DRAM (Dynamic Random Access Memory), an SRAM (Static Random Access Memory) or a flash memory (EEPROM; Electric Erasable Read Only Electric Erasable Read Only Memory) or the like, a semiconductor integrated circuit device with a logic circuit such as, e.g., a microprocessor or the like,

or a mixed-discrete-components-loaded type semiconductor circuit device in which the above-mentioned memory circuit and logic circuit are provided on one and the same semiconductor substrate.

5 Further, the technical concept of the present invention is not limited to the application to the method of manufacturing semiconductor integrated circuit devices but can also be applied to the method of manufacturing other electronic devices (electronic
10 circuit devices) etc. such as, e.g., a liquid crystal substrate and a magnetic head.

 Further, the pellicle is stuck or bonded to the mask substrate in the portion provided with no resist, whereby a good fixing characteristic is provided. In
15 particular, in case the pellicle is contact-fixed on a chromium (metal) screening film in the periphery of the mask, a specially excellent fixing characteristic is exhibited.

 Further, the fixing of the pellicle to the mask
20 holder of the mask is made in such a manner that the pellicle is contact-fixed onto that portion of the mask periphery which has no resist film, that is, onto the surface of a quartz mask substrate, a screening metal portion such as, e.g., chromium or a metal
25 compound film portion; and thus, a good fixing

characteristic followed by no shift or deviation is exhibited.

The effects achieved by the typical ones of the inventions disclosed in the present application will
5 be briefly described below.

(1). According to the present invention, in the periphery of the optical mask, any of various patterns comprising a resist film are not provided in the region with which the mounting portion of the
10 inspection equipment, the aligner or the like is contacted, whereby the occurrence of foreign matters due to the peeling-off or shaving-off of the resist film on the optical mask due to the mechanical shocks caused when the optical mask is mounted on the
15 inspection equipment, the aligner or the like can be suppressed or prevented.

(2). Due to foregoing Item (1), the deterioration of the detecting accuracy due to the peeling-off or shaving-off of the resist film on the
20 photo mask and the deterioration in the transfer accuracy of the exposure pattern can be prevented.

(3). Due to foregoing Item (1), it becomes possible to prevent the short-circuit defects, open-circuit defects, etc. between the patterns on the
25 semiconductor wafer due to the peeling-off or shaving-

off of the resist film on the photo mask.

(4). Since a light screening metal region is provided in the outer periphery of the mask substrate of the optical mask, and, by removing a portion of this light screening metal region, a mark pattern for detecting the information of the optical mask is formed, the ability of detecting the information of the optical mask can be enhanced.

(5). Due to foregoing Item (4), the detecting accuracy of the calibrating mark on the optical mask can be enhanced in case of inspecting the optical mask, so that the inspecting accuracy of the optical mask can be enhanced. Therefore, the reliability of the optical mask can be enhanced.

(6). Due to foregoing Item (4), the accuracy in the alignment between the optical mask and the aligner can be enhanced. Accordingly, the transfer accuracy of the patterns transferred onto the semiconductor wafer and the alignment accuracy can be enhanced.

(7). Due to foregoing Items (1) to (6), the reliability of the semiconductor integrated circuit devices manufactured by the use of the optical mask according to the present invention can be enhanced.

(8). Due to foregoing Items (1) to (6), the yield of the semiconductor integrated circuit devices

manufactured by the use of the optical mask according
to the present invention can be enhanced.



What is claimed is:

1. A method of manufacturing a semiconductor integrated circuit device, comprising: (a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a second major surface side of a mask substrate, said mask substrate having on a first major surface thereof a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern; and (b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through said mask substrate, whereby said integrated circuit pattern is imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer and thus transferred.

2. The method of manufacturing a semiconductor integrated circuit device according to Claim 1, wherein the wavelength of said exposure light is at least 100 nm less than 250 nm.

3. The method of manufacturing a semiconductor integrated circuit device according to Claim 2, wherein said wavelength of said exposure light is at least 100 nm but less than 200 nm.

4. The method of manufacturing a semiconductor integrated circuit device according to Claim 3,



wherein, in the peripheral portion of the first major surface of said mask substrate, a light screening metal region is provided.

5 5. The method of manufacturing a semiconductor integrated circuit device according to Claim 4, wherein, on the first major surface of said mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening metal region.

10 6. A method of manufacturing a semiconductor integrated circuit device, comprising:
 (a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of said mask substrate
15 in the state in which the peripheral region of said mask substrate is held on a mask holding mechanism, said mask substrate having on the first major surface thereof a light shielding pattern which is an integrated circuit pattern on a mask and comprises a
20 photo resist pattern, said resist pattern being not provided on said peripheral region; and
 (b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through said mask substrate, whereby said
25 integrated circuit pattern is imaged on a photo resist



film formed on a first major surface of a semiconductor integrated circuit wafer and thus transferred.

7. The method of manufacturing a semiconductor integrated circuit according to Claim 6, wherein the wavelength of said exposure light is at least 100 nm but less than 250 nm.

8. The method of manufacturing a semiconductor integrated circuit according to Claim 7, wherein, wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

9. The method of manufacturing a semiconductor integrated circuit device according to Claim 8, wherein, in the peripheral portion of the first major surface of said mask substrate, a light screening metal region is provided.

10. The method of manufacturing a semiconductor integrated circuit device according to Claim 9, wherein, on the first major surface of said mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening metal region.

11. A method of manufacturing a semiconductor integrated circuit device, comprising:
(a) the step of irradiating far ultraviolet or vacuum



ultraviolet exposure light from a first major surface or second major surface side of a mask substrate, said mask substrate having, in an integrated circuit pattern region of the first major surface thereof, a
5 light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern and having a light screening metal region provided in the peripheral region of said first major surface; and
(b) the step of reduction-projecting, by a projection
10 optical system, said exposure light which has transmitted through said mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus
15 transferred.

12. The method of manufacturing a semiconductor integrated circuit device according to Claim 11, wherein the wavelength of said exposure light is at least 100 nm but less than 250 nm.

20 13. The method of manufacturing a semiconductor integrated circuit device according to Claim 12, wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

14. The method of manufacturing a semiconductor
25 integrated circuit device according to Claim 13,



wherein, on the first major surface of said mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening metal region.

5 15. A method of manufacturing a semiconductor integrated circuit device, comprising:

(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of a mask substrate,
10 said mask substrate having, in an integrated circuit pattern region of the first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, wherein a pellicle is contact-fixed in that
15 part of the peripheral portion of said integrated circuit pattern region in which said photo resist pattern is not formed; and

(b) the step of reduction-projecting, by a projection optical system, said exposure light which has
20 transmitted through said mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus transferred.

25 16. The method of manufacturing a semiconductor



integrated circuit device according to Claim 15,
wherein the wavelength of said exposure light is at
least 100 nm but less than 250 nm.

17. The method of manufacturing a semiconductor
5 integrated circuit device according to Claim 16,
wherein the wavelength of said exposure light is at
least 100 nm but less than 200 nm.

18. The method of manufacturing a semiconductor
integrated circuit device according to Claim 17,
10 wherein, in the peripheral portion of the first major
surface of said mask substrate, a light screening
metal region is provided.

19. The method of manufacturing a semiconductor
integrated circuit device according to Claim 18,
15 wherein, on the first major surface of said mask
substrate, said pellicle is contact-fixed on said
light screening metal region.

20. A method of manufacturing a semiconductor
integrated circuit device, comprising:
20 (a) the step of irradiating far ultraviolet or vacuum
ultraviolet exposure light from a first major surface
side or a second major surface side of a mask
substrate, said mask substrate having, on the first
major surface thereof, a halftone light shielding
25 pattern comprising a photo resist pattern which



constitutes an integrated circuit pattern on a mask;

and

(b) the step of reduction-projecting, by a projection optical system, said exposure light which has

5 transmitted through said mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus transferred.

10 21. The method of manufacturing a semiconductor integrated circuit device according to Claim 20, wherein the wavelength of said exposure light is at least 100 nm but less than 250 nm.

15 22. The method of manufacturing a semiconductor integrated circuit device according to Claim 21, wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

20 23. The method of manufacturing a semiconductor integrated circuit device according to Claim 22, wherein, in the peripheral portion of the first major surface of said mask substrate, a light screening metal region is provided.

25 24. The method of manufacturing a semiconductor integrated circuit device according to Claim 23, wherein, on the first major surface of said mask



substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening region.

25. A method of manufacturing a semiconductor integrated circuit device, comprising:
5 (a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface side or a second major surface side of a mask substrate, which has, on the first major surface
10 thereof, a light shielding pattern which is an integrated circuit pattern on a Lebenson type phase shift mask and comprises a photo resist pattern; and
(b) the step of reduction-projecting, by a projection optical system, the exposure light which has
15 transmitted through said mask substrate, whereby, on a first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus transferred.

26. The method of manufacturing a semiconductor integrated circuit device according to Claim 25,
20 wherein the wavelength of said exposure light is at least 100 nm but less than 250 nm.

27. The method of manufacturing a semiconductor integrated circuit device according to Claim 26,
25 wherein, wherein the wavelength of said exposure light



is at least 100 nm but less than 200 nm.

28. The method of manufacturing a semiconductor integrated circuit device according to Claim 27, wherein, in the peripheral portion of said first major surface, a light screening metal region is provided.

29. The method of manufacturing a semiconductor integrated circuit device according to Claim 28, wherein, on the first major surface of said mask substrate, a pellicle is provided so as to cover said integrated circuit pattern, said pellicle being contact-fixed on said light screening metal region.

30. A method of manufacturing a semiconductor integrated circuit device, comprising:
(a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of a mask substrate, said mask substrate having, in an integrated circuit pattern region of said first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, wherein a pellicle is contact-fixed in the peripheral portion of said integrated circuit pattern of said first major surface so as to cover said integrated circuit pattern; and
(b) the step of reduction-projecting, by a projection



optical system, said exposure light which has
transmitted through said mask substrate, whereby, on a
photo resist film formed on a first major surface of a
semiconductor integrated circuit, said integrated
5 circuit pattern is imaged and thus transferred.

31. The method of manufacturing a semiconductor
integrated circuit device according to Claim 30,
wherein the wavelength of said exposure light is at
least 100 nm but less than 250 nm.

10 32. The method of manufacturing a semiconductor
integrated circuit device according to Claim 31,
wherein the wavelength of said exposure light is at
least 100 nm but less than 200 nm.

33. The method of manufacturing a semiconductor
15 integrated circuit device according to Claim 32,
wherein, in the peripheral portion of the first major
surface of said mask substrate, a light screening
metal region is provided.

34. The method of manufacturing a semiconductor
20 integrated circuit device according to Claim 33,
wherein, on the first major surface of said mask
substrate, a pellicle is provided so as to cover said
integrated circuit pattern, said pellicle being
contact-fixed on said light screening metal region.

25 35. A method of manufacturing a semiconductor



integrated circuit device, comprising:

- (a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of a mask substrate, said mask substrate having, in an integrated circuit pattern region of said first major surface thereof, a light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, wherein a protective film is formed on said photo resist pattern so as to cover said integrated circuit pattern region of said first major surface; and
- (b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through said mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, said integrated circuit pattern is imaged and thus transferred.

36. The method of manufacturing a semiconductor integrated circuit device according to Claim 35, wherein the wavelength of said exposure light is at least 100 nm but less than 250 nm.

37. The method of manufacturing a semiconductor integrated circuit device according to Claim 36,



wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

38. A method of manufacturing a semiconductor integrated circuit device, comprising:

- 5 (a) the step of irradiating far ultraviolet or vacuum ultraviolet exposure light from a first major surface or a second major surface side of a mask substrate, said mask substrate having, in an integrated circuit pattern region of said first major surface thereof, a
10 light shielding pattern which is an integrated circuit pattern on a mask and comprises a photo resist pattern, wherein a conductive ground film is formed beneath said photo resist pattern on said first major surface; and
- 15 (b) the step of reduction-projecting, by a projection optical system, said exposure light which has transmitted through said mask substrate, whereby, on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, said
20 integrated circuit pattern is imaged and thus transferred.

39. The method of manufacturing a semiconductor integrated circuit device according to Claim 38, wherein the wavelength of said exposure light is at
25 least 100 nm but less than 250 nm.



40. The method of manufacturing a semiconductor integrated circuit device according to Claim 39, wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

5 41. Mask blanks for the reduction projection exposure of vacuum ultraviolet rays, comprising:
 (a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet rays or vacuum ultraviolet rays with a
10 wavelength of at least 100 nm but less than 250 nm;
 (b) a region coated with a light screening metal film which region is formed on said first major surface of said mask substrate; and
 (c) an opening region provided in the portion
15 corresponding to an integrated circuit pattern region in the central portion of said region coated with a light screening metal film.

20 42. The method of manufacturing a semiconductor integrated circuit device according to Claim 41, wherein the wavelength of said exposure light is at least 100 nm but less than 200 nm.

25 43. A method of manufacturing an optical mask for performing the reduction projection exposure of a semiconductor integrated circuit device, wherein far ultraviolet rays or vacuum ultraviolet rays are used



as the exposure light, comprising:

(a) the step of placing a mask substrate on a processed-mask holding portion of a mask writer;

5 (b) the step of detecting a position detecting pattern provided in the peripheral portion of a first major surface of said mask substrate; and

(c) the step of calibrating an integrated circuit pattern to the position where it is to be written, on the basis of the result of the above-mentioned
10 detection, whereby said integrated circuit pattern is written on an integrated circuit pattern region on said first major surface.

44. The method of manufacturing a semiconductor integrated circuit device according to Claim 43,
15 wherein the wavelength of said exposure light is at least 100 nm but less than 250 nm.

45. The method of manufacturing a semiconductor integrated circuit device according to Claim 44,
wherein the wavelength of said exposure light is at
20 least 100 nm but less than 200 nm.

46. An optical mask comprising:

(a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet or vacuum ultraviolet rays;

25 (b) an integrated circuit pattern region of the first



major surface of said mask substrate;

(c) an integrated circuit pattern on the mask substrate, said integrated circuit pattern being formed of a light shielding pattern in said integrated circuit pattern region of said mask substrate and being imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through said mask substrate, said integrated circuit pattern being thus transferred; and (d) a light screening metal region provided in the peripheral region of the first major surface of said mask substrate.

47. An optical mask comprising:

(a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet or vacuum ultraviolet rays;

(b) an integrated circuit pattern region of the first major surface of said mask substrate; and

(c) an integrated circuit pattern on the mask substrate, said integrated circuit pattern being formed, in said integrated circuit pattern region of said mask substrate, of a halftone light shielding pattern which comprises a photo resist pattern, said



integrated circuit pattern being imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through said mask substrate, said integrated circuit pattern being thus transferred.

48. An optical mask comprising:

(a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet or vacuum ultraviolet rays;

(b) a Lebenson type phase shift means formed on said first major surface or second major surface;

(c) an integrated circuit pattern region of the first major surface of said mask substrate; and

(d) an integrated circuit pattern on a mask substrate, said integrated circuit pattern being formed, in said integrated circuit pattern region of said mask substrate, of a light shielding pattern which

comprises a photo resist pattern, said integrated circuit pattern being imaged on a photo resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through said mask



substrate, said integrated circuit pattern being thus transferred.

49. An optical mask comprising:

(a) a mask substrate which has first and second major surfaces and is transparent with respect to far ultraviolet rays or vacuum ultraviolet rays;

(b) an integrated circuit pattern region of the first major surface of said mask substrate;

(c) an integrated circuit pattern on the mask

substrate, said integrated circuit pattern being formed, in said integrated circuit pattern region of said mask substrate, of a halftone light shielding pattern which comprises a photo resist pattern, said integrated circuit pattern being imaged on a photo

resist film formed on a first major surface of a semiconductor integrated circuit wafer, by reduction-projecting, by means of a projection optical system, the exposure light which has transmitted through said mask substrate, said integrated circuit pattern being thus transferred; and

(d) a protective film covering said integrated circuit pattern region and said light shielding pattern.